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The Substitution of a Semi-infinite,  
Homogeneous Dielectric Medium  
for a Plasma Slab

S. Gotkis

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30 April 1966

Prepared for:  
National Aeronautics and Space Administration  
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Department of ELECTRICAL ENGINEERING



THE OHIO STATE UNIVERSITY  
RESEARCH FOUNDATION  
Columbus, Ohio

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REPORT

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COLUMBUS, OHIO 43212

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Submitted by	S. Gotkis Antenna Laboratory Department of Electrical Engineering
Date	30 April 1966

## ABSTRACT

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The substitution of a homogeneous, semi-infinite dielectric for a finite plasma slab is studied as a means of simplifying the analyses of the impedance of an aperture antenna radiating into an inhomogeneous plasma medium. Such a substitution could be made if the reflection coefficients of the equivalent medium, as a function of angle of incidence, corresponded to the reflection coefficients of the plasma slab. The dielectric constant of the equivalent medium is found by matching reflection coefficients at some particular angle of incidence (usually  $0^\circ$ ). The range of angular correspondence is narrow (less than  $5^\circ$ ) for cases in which the dielectric constant dips to near or below zero. In other cases fairly wide ranges of equivalence occur.

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# THE SUBSTITUTION OF A SEMI-INFINITE, HOMOGENEOUS DIELECTRIC MEDIUM FOR A PLASMA SLAB

## INTRODUCTION

It is generally quite difficult to determine the impedance of an aperture antenna in the presence of an inhomogeneous layered plasma medium. One of the major difficulties is treating the inhomogeneous plasma itself. The problem would be greatly simplified if the inhomogeneous plasma could be approximated by some homogeneous, semi-infinite dielectric. The problem of an aperture antenna radiating into a semi-infinite, homogeneous medium is much easier to solve. For example, the case of an open-ended rectangular waveguide in which the interface of the semi-infinite medium is coincident with the guide aperture has been analyzed.<sup>1</sup>

The purpose of this report is to describe a manner in which the homogeneous, semi-infinite dielectric can be substituted for the inhomogeneous plasma. If the plane wave reflection coefficients of the homogeneous half-space are equivalent, as a function of the incidence angle, to the reflection coefficients of the original inhomogeneous plasma, the homogeneous dielectric can be substituted over the range of equivalence. The validity of this approximation may be determined by first calculating the plane wave reflection coefficients as a function of angle of incidence for the inhomogeneous plasma layer. Then at some arbitrary incidence angle (usually  $0^\circ$ ) the reflection coefficient is matched to that of a homogeneous dielectric medium with the appropriate dielectric constant.

Once the value of the dielectric constant of the semi-infinite medium has been determined so that the reflection coefficients of the two media match for that incidence, the reflection coefficients are calculated for the homogeneous medium. For cases in which these reflection coefficients approximate well those of the inhomogeneous plasma, the homogeneous medium may be substituted for the plasma.

It is anticipated that the semi-infinite dielectric can be so chosen that reflection coefficients will coincide over a wide enough angular range to be of practical use. This would be useful for an antenna aperture somewhat removed from the face of the plasma layer. Such conditions exist during the re-entry of a space vehicle into the atmosphere. The gap between the antenna aperture and the plasma sheath is often on the order of a wavelength.

## DIELECTRIC SLABS

To initially calculate the plane wave reflection coefficients of inhomogeneous media, computer programs were written for both parallel and perpendicular polarizations. The calculations were based on a technique by Richmond<sup>2</sup> where the fields are computed at intervals in the medium by a recursion process. Then the reflection coefficients are found from the computed fields. The programs are shown in Appendix A, Figs. 32 and 33.

Use of these programs revealed several limitations. Care must be taken to keep the distance between points of calculation as small as possible for the recursion technique to be effective. Also variation in the dielectric constant from point to point must not be too great. When the variations in the dielectric constant are large the program calculates transmission coefficients greater than unity. The programs are ineffective for cases in which the relative dielectric constants,  $\epsilon_r$ , are equal to zero or varied near zero. The formulation is also inaccurate for negative dielectric constants.

As a result another program based on a new technique by Richmond<sup>3</sup> was written. This program is based on the exact field solutions for a layered medium. Recursion techniques are used to solve for the exact fields and the reflection coefficients. Both cases, parallel and perpendicular polarization, are handled simultaneously. Two versions of this program were written. In one version calculations are made directly from dielectric constants which are read in for each layer. In a second version electron density and collision frequency profiles are introduced and the resultant complex dielectric constant is calculated and then used. The new programs are accurate in all regions, including the regions in which the original programs were limited. In Figs. 34 and 35 (Appendix A) the statement listings are given for both versions of the program. The results presented in this report were calculated by the new programs.

The equations for plane wave reflection from a semi-infinite medium are used to determine the properties of the equivalent medium. The dielectric constant of the equivalent semi-infinite medium is determined by matching its reflection coefficient with that of the original medium for some particular angle of incidence (usually  $0^\circ$ ). Then the reflection coefficients of the two media are compared as a function of the incidence angle. If the two coefficients agree over a sufficiently wide range of incidence, the equivalent semi-infinite medium may be substituted for the original medium. The range of agreement may not have to be more than  $20^\circ$ - $30^\circ$  because of the corresponding pattern of

the antenna whose impedance is to be determined.

The equations for plane wave reflection from a semi-infinite medium are given by

$$(1) \quad R = \frac{\cos \theta - \sqrt{\epsilon_r - \sin^2 \theta}}{\cos \theta + \sqrt{\epsilon_r - \sin^2 \theta}} \quad (\text{perpendicular polarization})$$

and

$$(2) \quad R = - \frac{\epsilon_r \cos \theta - \sqrt{\epsilon_r - \sin^2 \theta}}{\epsilon_r \cos \theta + \sqrt{\epsilon_r - \sin^2 \theta}} \quad (\text{parallel polarization}),$$

where  $\epsilon_r$  is the relative dielectric constant and  $\theta$  is the angle of incidence.

To demonstrate the validity of the equivalent medium technique several dielectric constant distributions were analyzed. In Figs. 1-5 comparisons are given of the reflections from dielectric slabs with uniform dielectric constants with those of the equivalent media. In each case the polarization of the electric field is perpendicular to the plane of incidence. The angle at which the reflection coefficients of the slab and equivalent medium are matched is  $0^\circ$  in each case. The slabs are of constant thickness, with  $kd = 2.0$ .

The dielectric constant for Fig. 1 is  $\epsilon = -0.2$ , with reflection ranging from 0.77 to 1.0. The equivalent medium has a low dielectric constant of 0.01716 and hence matches only near  $0^\circ$  because the critical angle of total internal reflection is reached almost immediately. The critical angle of the equivalent medium occurs for  $\sin \theta_c = \sqrt{\epsilon_r}$  and is equal to  $7.52^\circ$  in Fig. 1.

Figure 2 is similar, with the dielectric constant of the uniform slab as  $\epsilon = 0.1$ . The value of the dielectric constant for the equivalent medium is 0.059 for which the critical angle of the equivalent medium occurs at  $14.06^\circ$ . Again the equivalent medium reflection coefficients correspond to those of the slab only in the neighborhood of  $0^\circ$ . Figure 3 is a plot with a slab dielectric constant of  $\epsilon = 0.2$ . The dielectric constant of the equivalent medium is 0.088 and the critical angle occurs at  $17.25^\circ$ . The equivalent medium reflection coefficients correspond to those of the slab for about  $10^\circ$ .

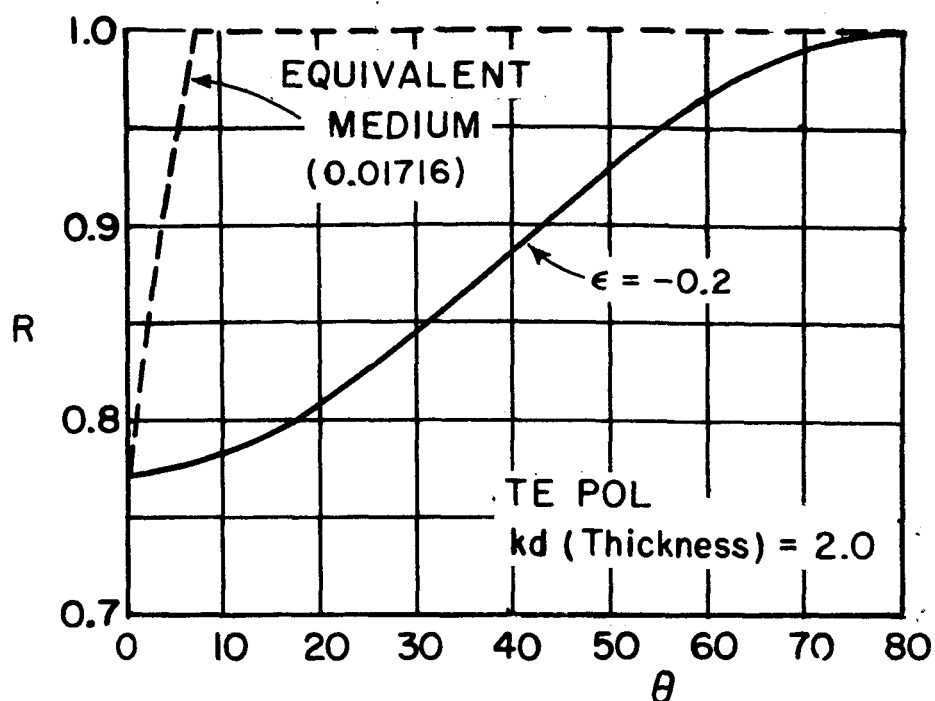


Fig. 1. Reflection vs incidence angle.

In Fig. 4 the uniform dielectric constant of the slab is  $\epsilon = 0.5$ . The value of the dielectric for the equivalent medium is  $\epsilon = 0.265$  and the critical angle is  $31^\circ$ . The reflection coefficients of the slab and equivalent medium agree for about a  $0^\circ$ - $20^\circ$  range. In Fig. 5 the dielectric constant of the slab is  $\epsilon = 0.8$  and that of the equivalent medium is  $\epsilon = 0.64$ . In this case the dielectric constant of the equivalent medium is near that of the slab and the critical angle does not occur until  $\theta_c = 53.13^\circ$ . The respective reflection coefficients correspond closely over a range of  $0^\circ$ - $40^\circ$ . In Figs. 1-5 it is seen that as the value of the dielectric constant of the equivalent medium increases and the critical angle becomes greater, there is a greater range of reflection coefficient correspondence and the equivalent medium concept becomes more meaningful.

Figures 6-10 contain data for slabs of uniform dielectric constant with an incident plane wave E-field polarization parallel to the plane of incidence. The thicknesses of the slabs are again constant, with  $kd = 2.0$ . In Fig. 6 the dielectric constant of the slab is negative with  $\epsilon = -0.2$ . The reflection coefficients for this negative medium demonstrate no Brewster angle as might be expected for parallel polarization. The dielectric constant of the equivalent medium and the critical angle are the same as for the perpendicular case with



with  $\epsilon = 0.01716$  and  $\theta_c = 7.52^\circ$ . The respective reflection coefficients match only at  $0^\circ$ .

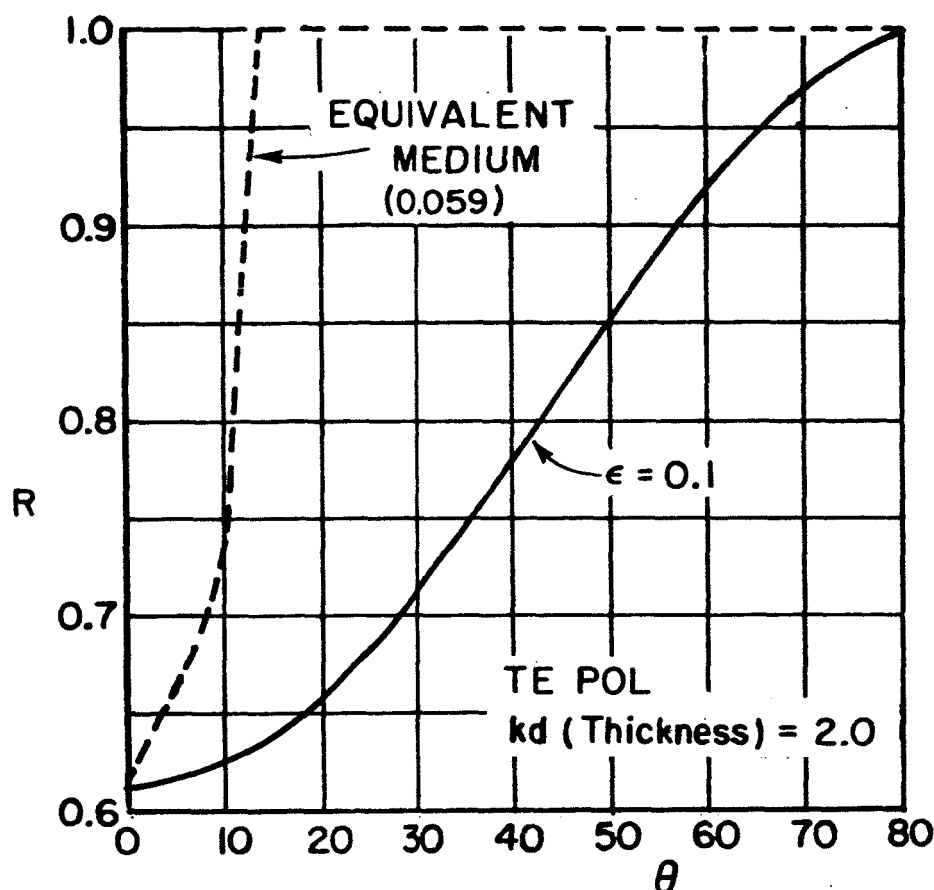


Fig. 2. Reflection vs incidence angle.

For Fig. 7 the slab dielectric constant is  $\epsilon = 0.1$  and that of the equivalent medium is  $\epsilon = 0.059$ . The critical angle is  $14.06^\circ$  and reflection coefficients correspond to near that point. The reflection coefficient of the slab rapidly approaches unity after passing through the Brewster angle of zero reflection. In Fig. 8 the dielectric constants of the slab and equivalent medium are, respectively,  $\epsilon = 0.2$  and  $\epsilon = 0.088$ . The critical angle is  $17.25^\circ$  and the reflection coefficients correspond over a range greater than  $0^\circ$ - $10^\circ$ . In Fig. 9 the dielectric constant of the slab is  $\epsilon = 0.5$  and that of the equivalent medium is  $\epsilon = 0.265$ . The critical angle is  $31^\circ$  and there is excellent correspondence of reflection coefficients to that point. For Fig. 10 the respective dielectric constants are for the uniform slab  $\epsilon = 0.8$ , and for the equivalent medium  $\epsilon = 0.64$ . The critical angle occurs at  $\theta_c = 53.13^\circ$  and the reflection coefficients correspond over a  $40^\circ$  range.

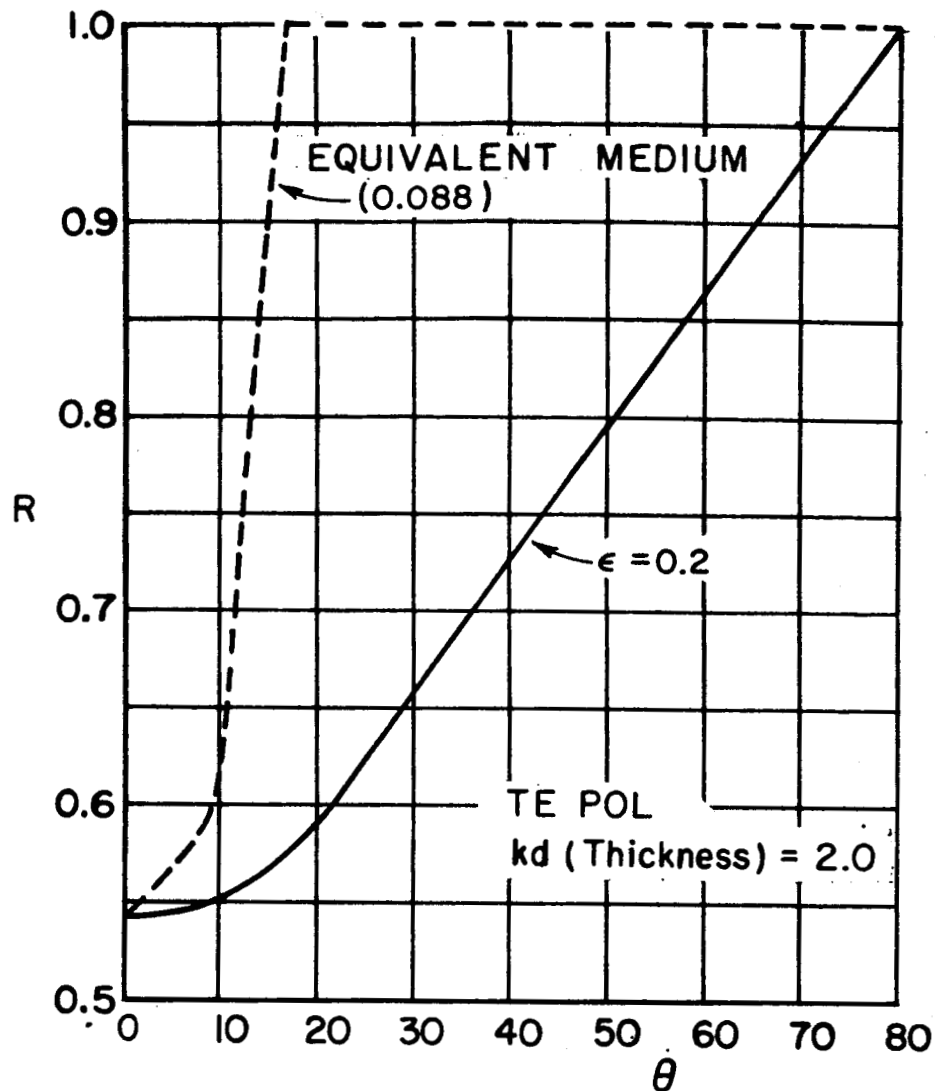


Fig. 3. Reflection vs incidence angle.

For either parallel or perpendicular polarizations, the critical angle becomes greater with increasing dielectric constant of the slab. For slabs with a low dielectric constant, such as  $\epsilon = -0.2$  or  $\epsilon = 0.1$ , the critical angle is reached immediately as the angle of incidence varies from the normal. The equivalent medium concept is more useful where the dielectric constants are greater, and that of the equivalent medium is more nearly equal to that of the slab.

Thus far only the magnitudes of the reflection coefficients have been considered. The phase of the reflection coefficients of the uniform dielectric slab and the equivalent medium will be compared for two cases

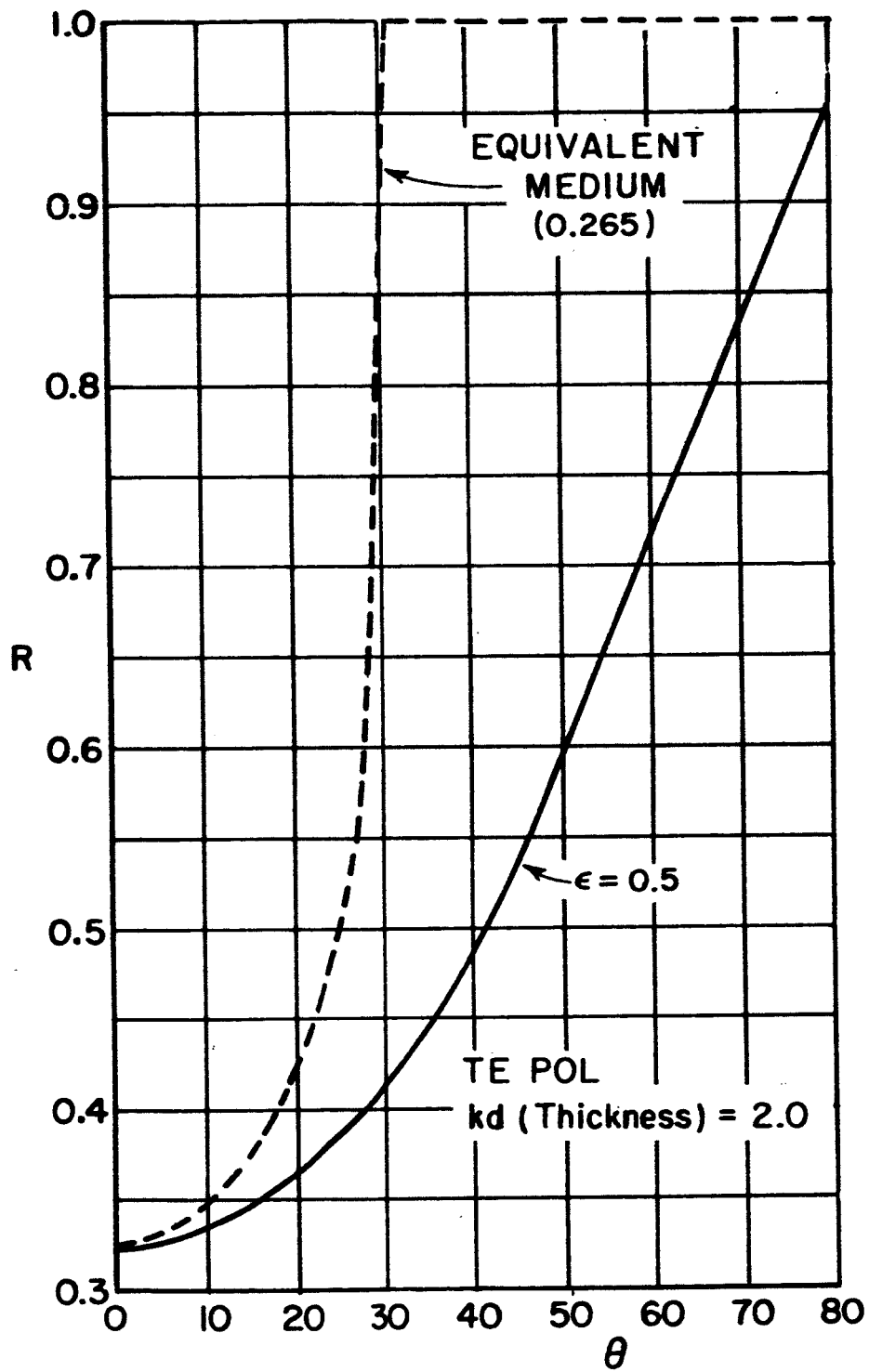


Fig. 4. Reflection vs incidence angle.

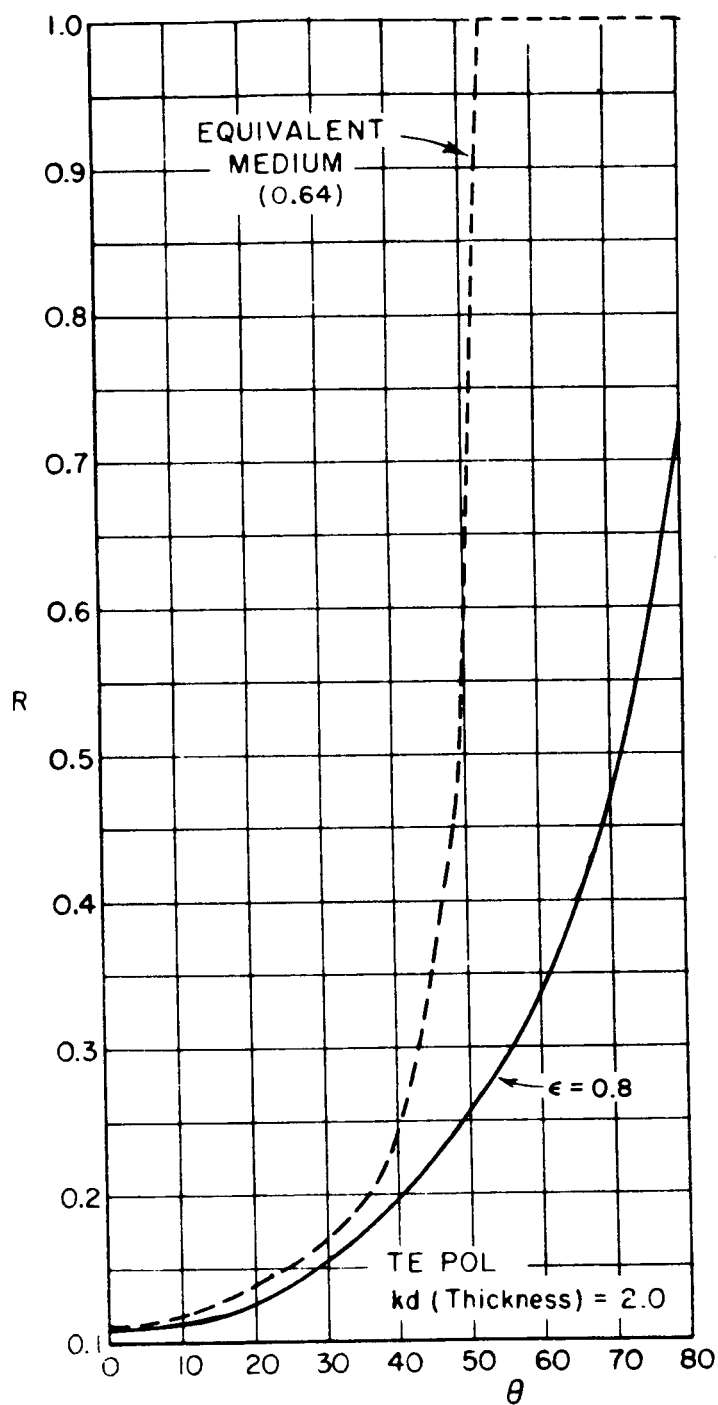


Fig. 5. Reflection vs incidence angle.

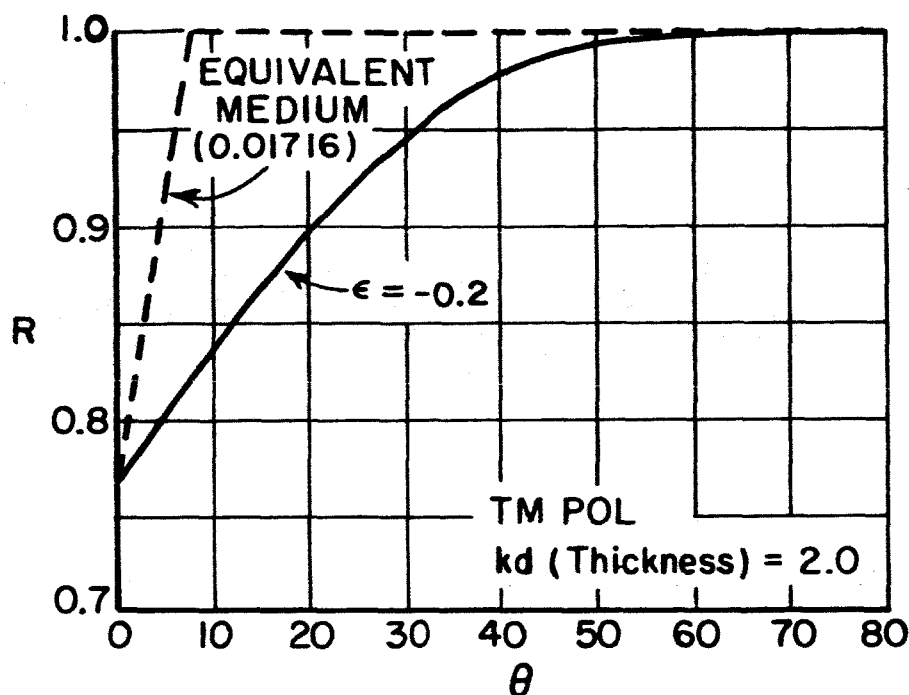


Fig. 6. Reflection vs incidence angle.

where the magnitudes correspond over a wide range. The two cases are for slabs of dielectric constant  $\epsilon = 0.5$  and  $\epsilon = 0.8$ .

Figure 11 represents a slab dielectric constant of  $\epsilon = 0.5$  and perpendicular polarization. It is seen that the relative phase angles of the reflection coefficients of the uniform slab and equivalent medium are very close for a range of approximately  $30^\circ$ . This correspondence of relative phase angles covers about the same range as the magnitude correspondence shown in Fig. 4. Figure 12 represents a uniform slab of  $\epsilon = 0.5$  and parallel polarization. The relative phase angles of the reflection coefficients of the slab and equivalent medium are in agreement for a range of over  $20^\circ$ . This agrees with the reflection coefficient magnitude correspondence of Fig. 9.

Figures 13 and 14 show reflection coefficient phase angles for a uniform dielectric slab of  $\epsilon = 0.8$  for perpendicular and parallel polarizations, respectively. In both cases the phase angle of the equivalent medium reflection coefficient is nearly equal to that of the slab for approximately  $40^\circ$ . As seen in Figs. 5 and 10 the magnitudes of the reflection coefficients agree over a similar range. Figures 11-14 demonstrate that where there is good correspondence in the reflection coefficient magnitudes of the slab and equivalent medium, the relative phase angles also agree.

Figures 15-19 give the reflection coefficient as a function of slab thickness for the dielectric slabs already discussed. The only case considered was that of parallel polarization. The reflection coefficients were analyzed for two angles of incidence,  $\theta = 0^\circ$  and  $\theta = 30^\circ$ . The dielectric constants of the slabs are, respectively,  $\epsilon = -0.2, 0.1, 0.2, 0.5$ , and  $0.8$ . As expected the reflection coefficients increase with increasing layer thickness. Also the reflection coefficients generally decrease with increasing dielectric constant.

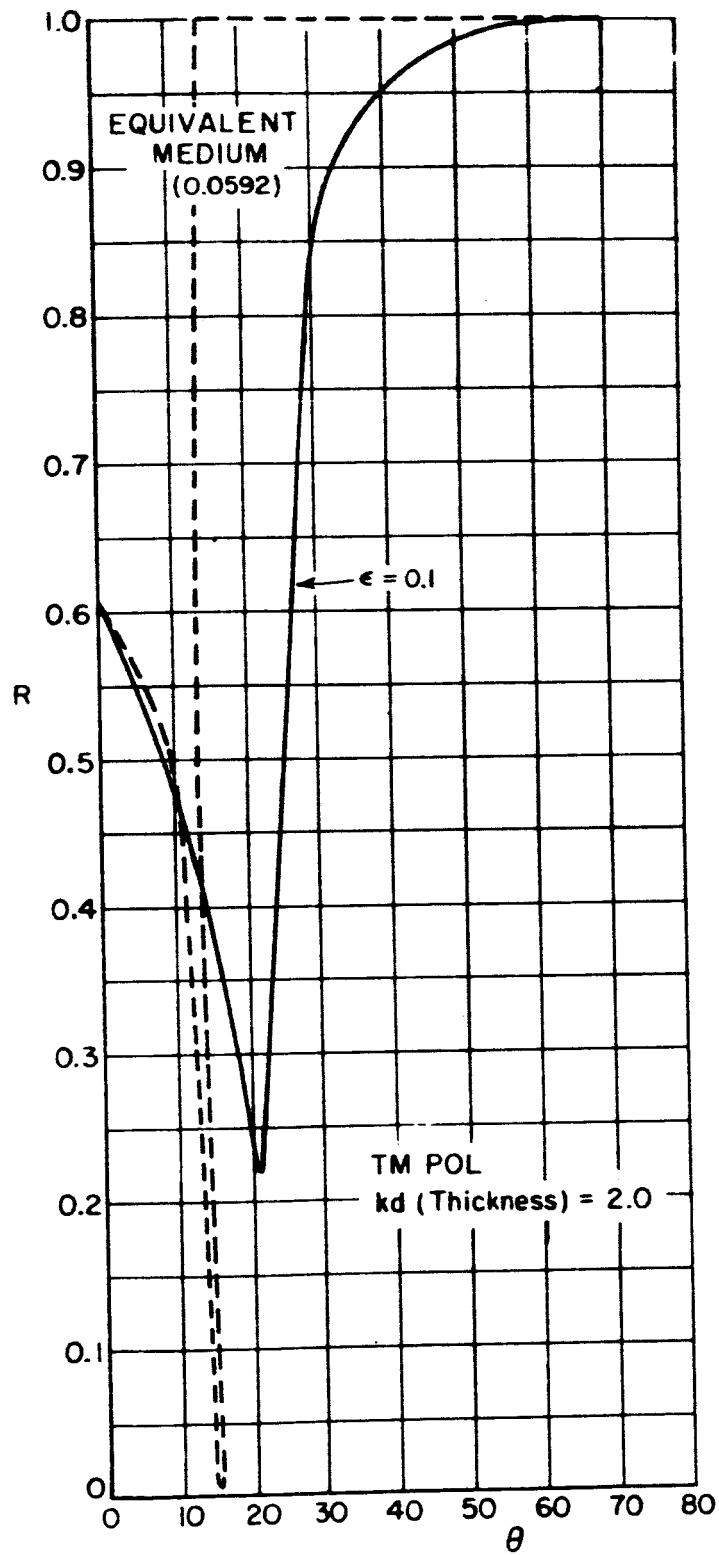


Fig. 7. Reflection vs incidence angle.

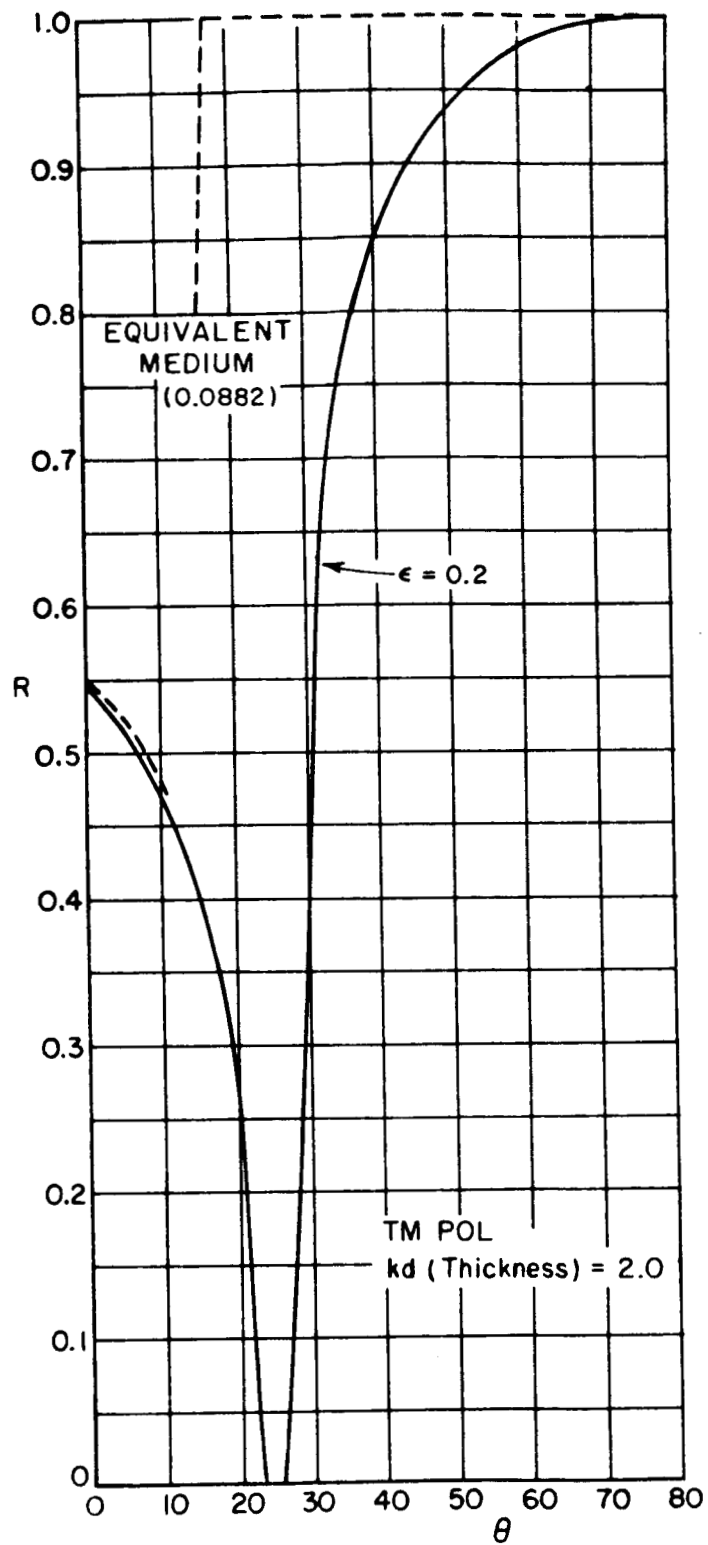


Fig. 8. Reflection vs incidence angle.



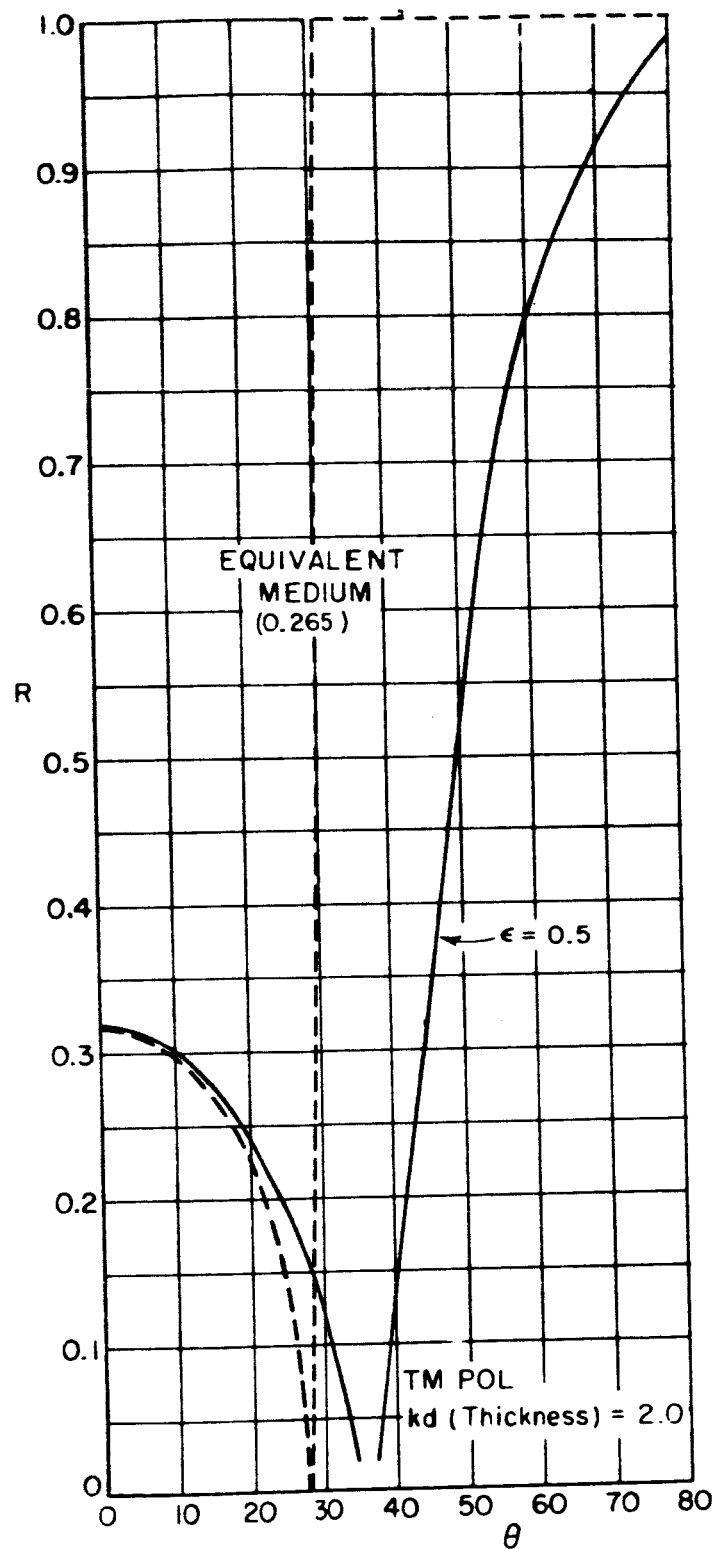


Fig. 9. Reflection vs incidence angle.

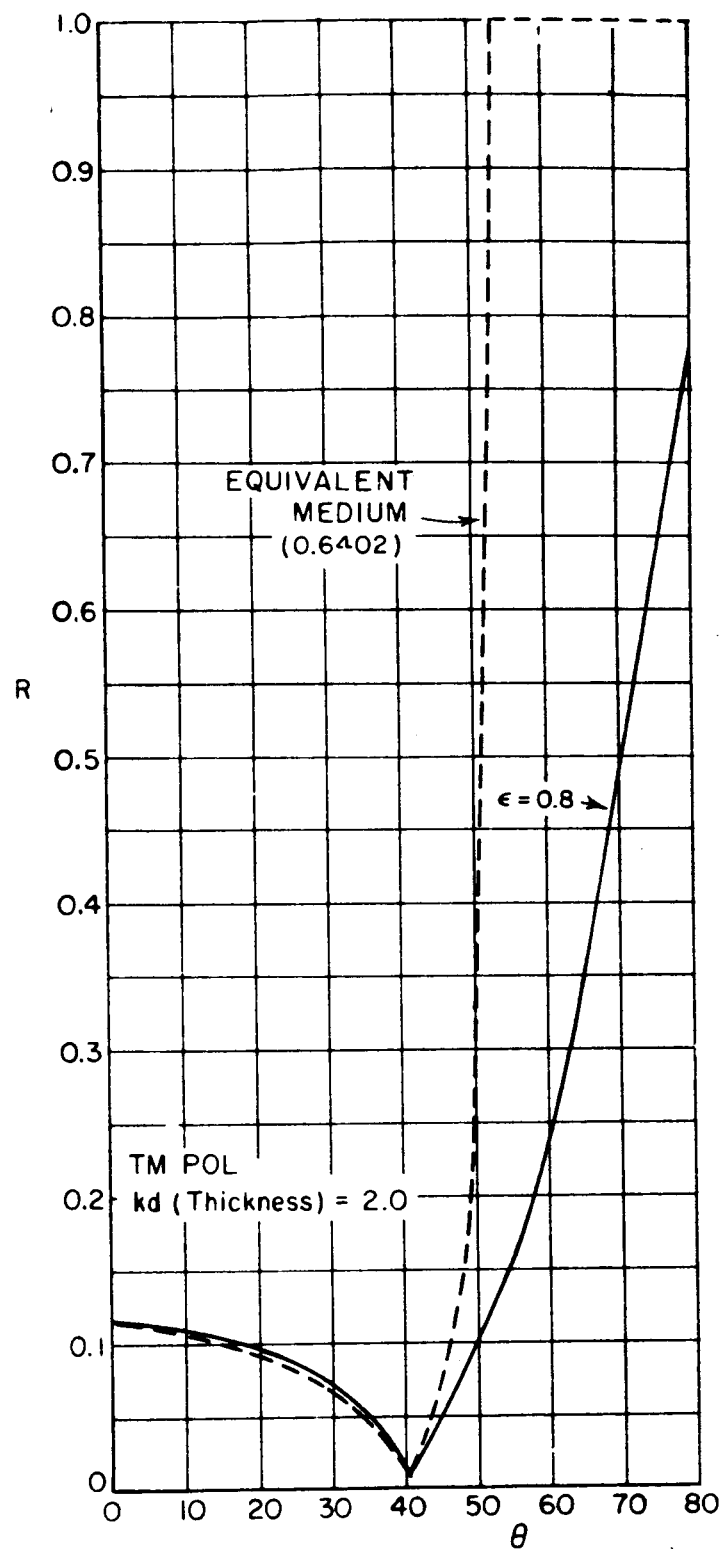


Fig. 10. Reflection vs incidence angle.

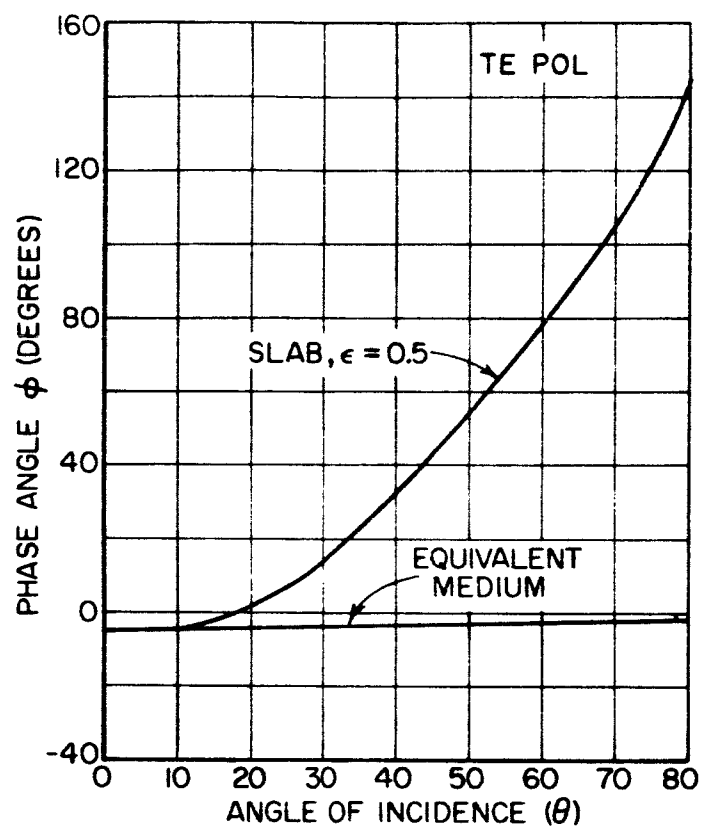


Fig. 11. Phase vs incidence angle.

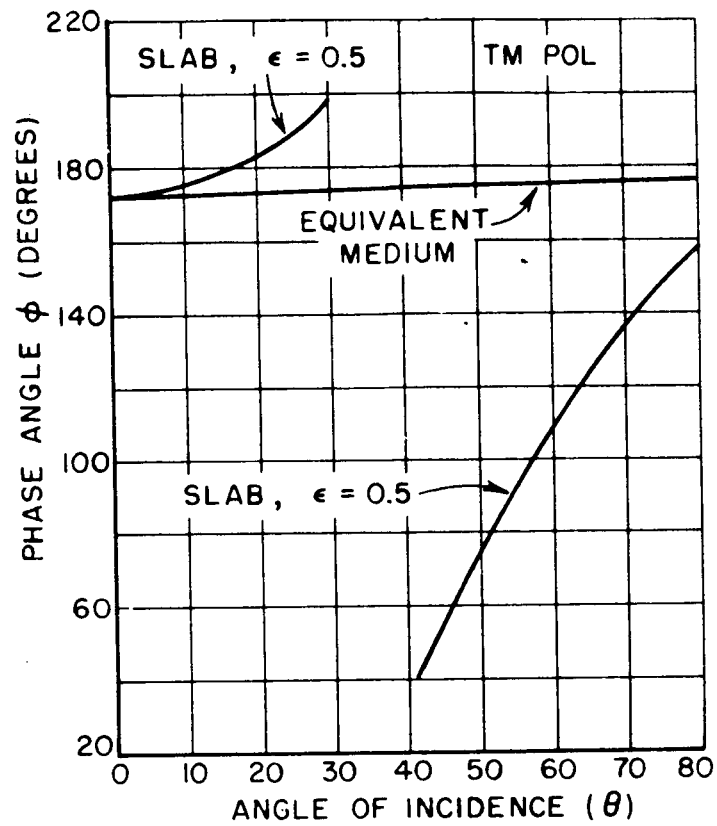


Fig. 12. Phase vs incidence angle.

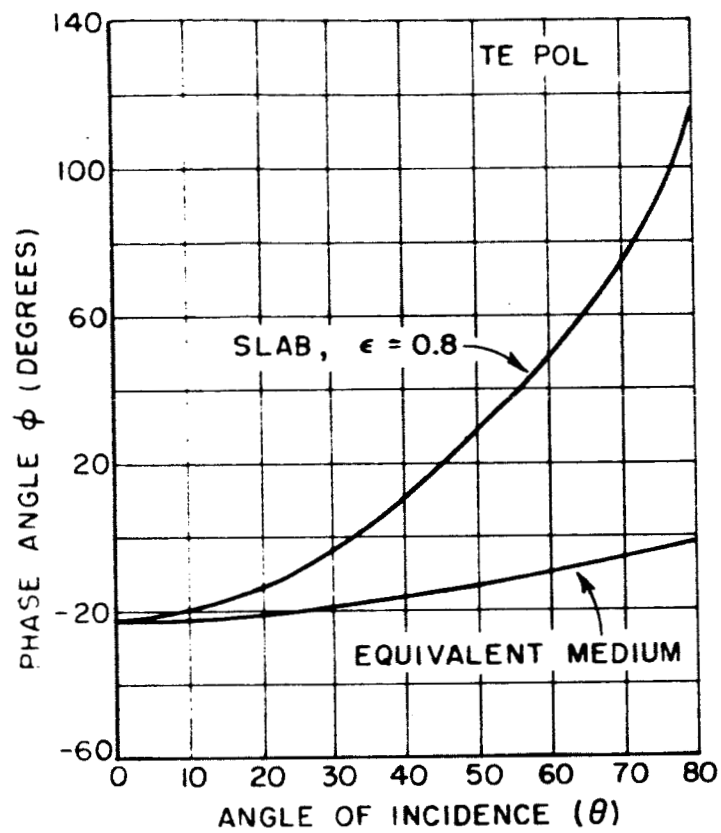


Fig. 13. Phase vs incidence angle.

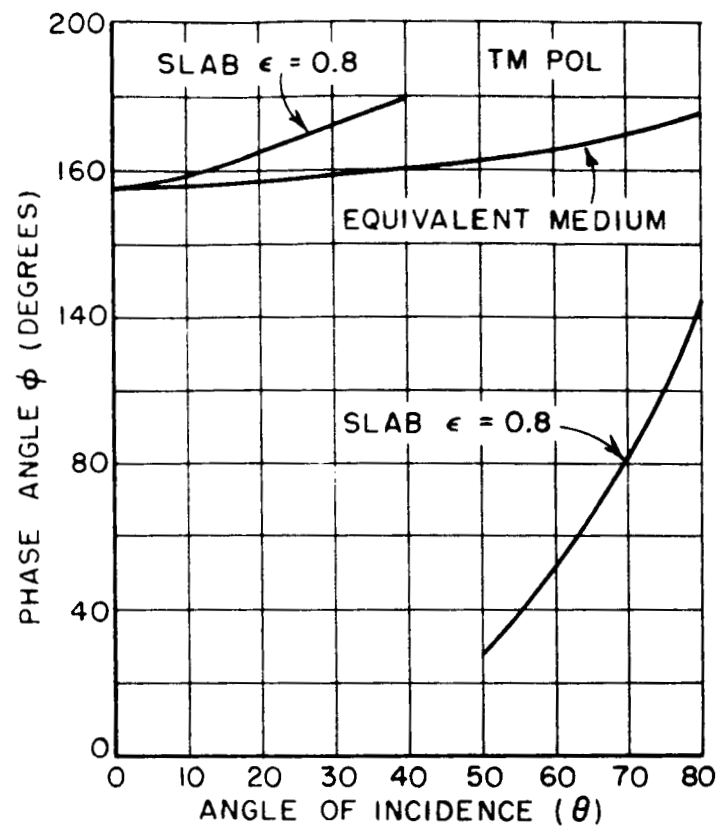


Fig. 14. Phase vs incidence angle.

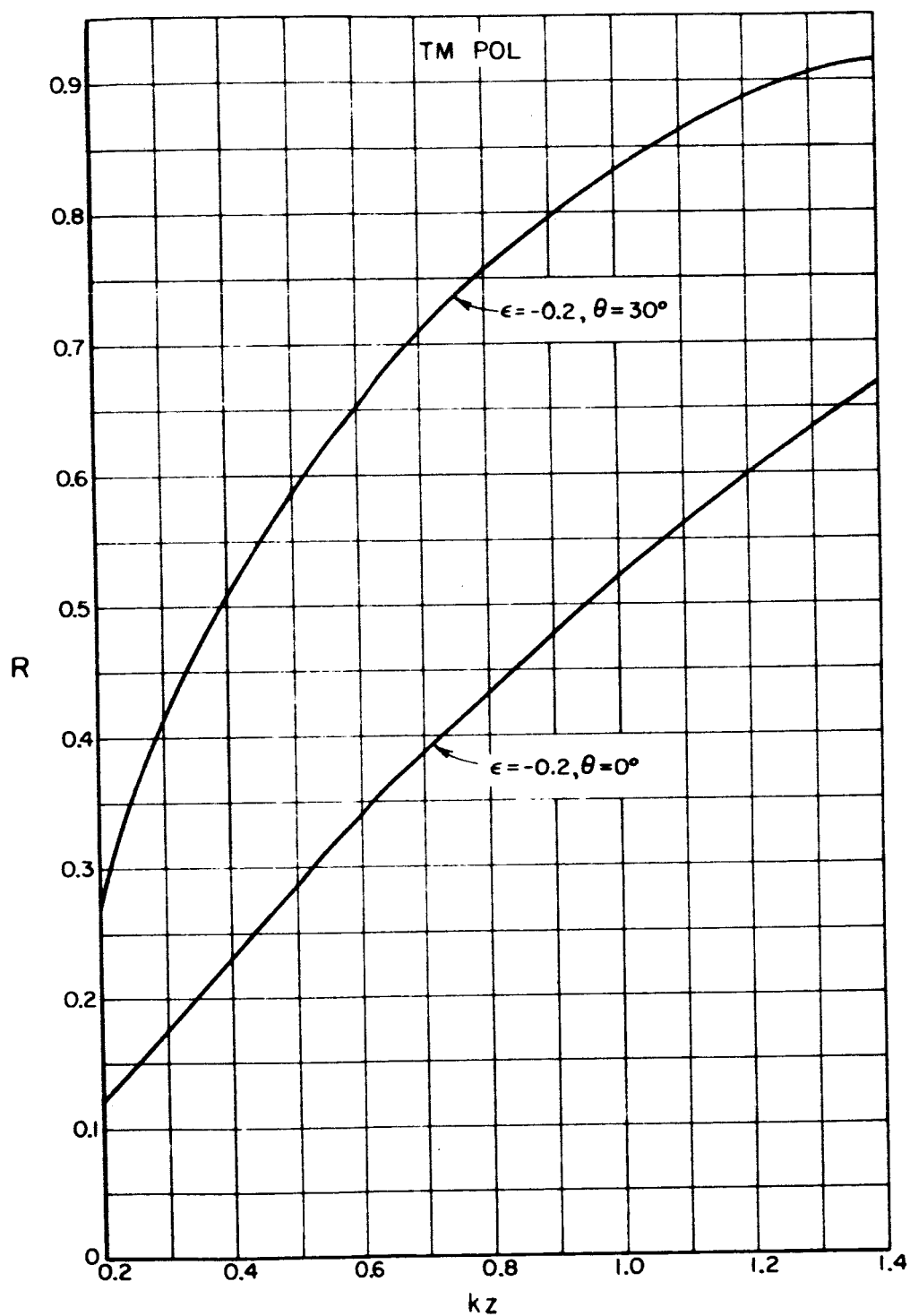


Fig. 15. Reflection coefficient vs layer thickness.

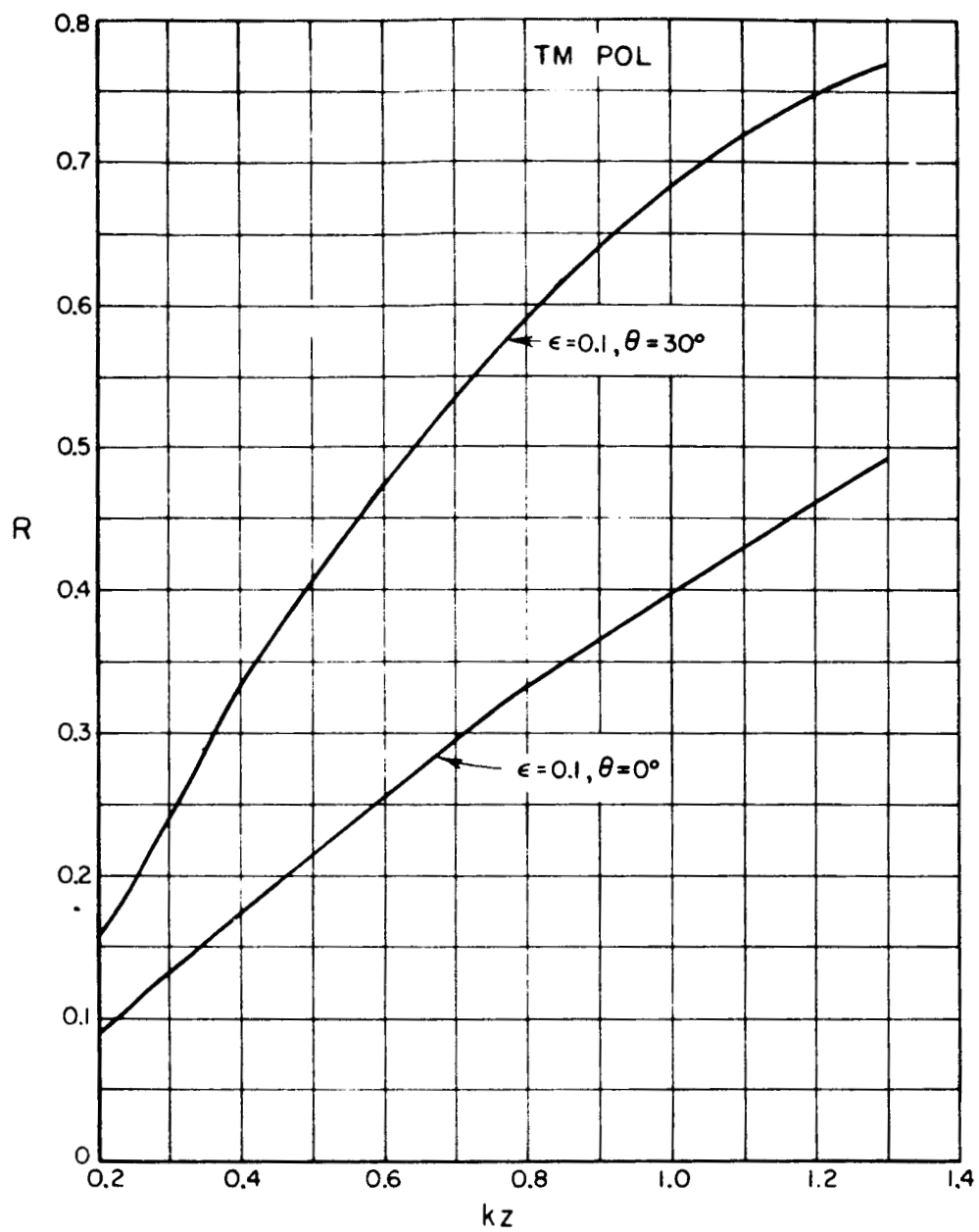


Fig. 16. Reflection coefficient vs layer thickness.



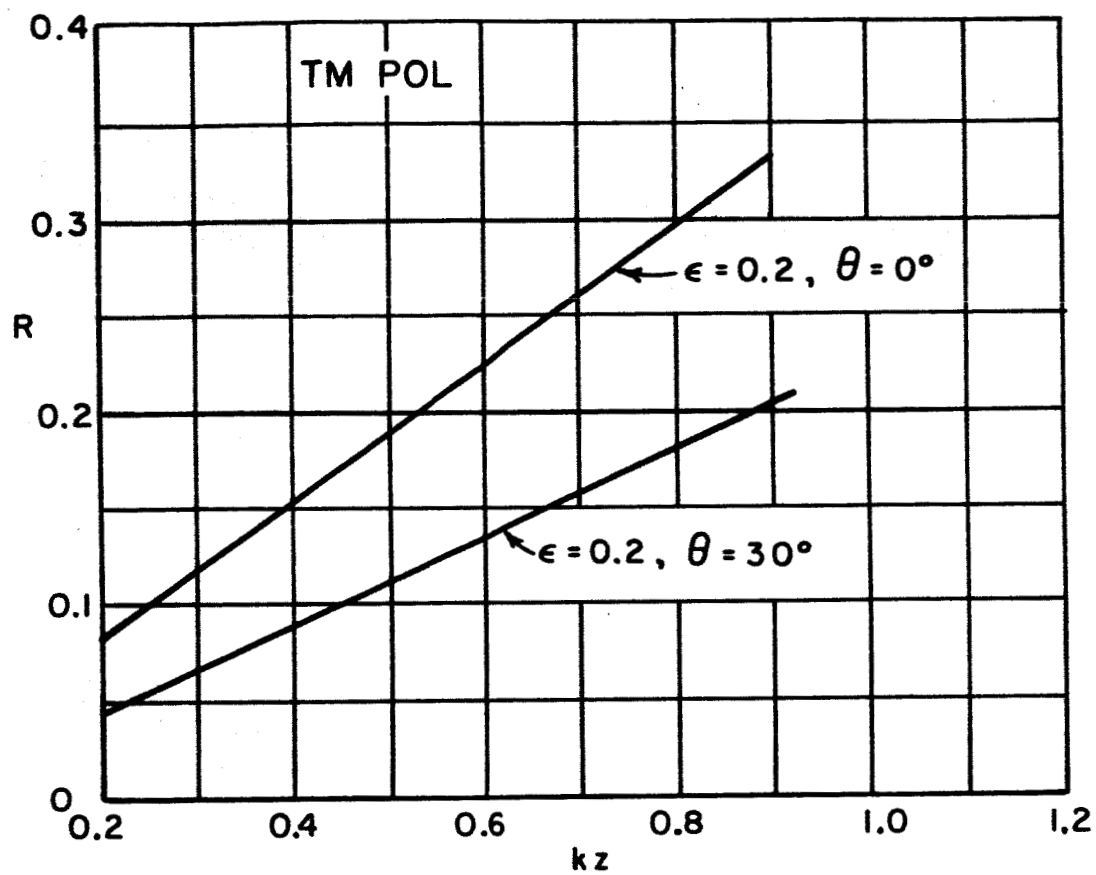


Fig. 17. Reflection coefficient vs layer thickness.

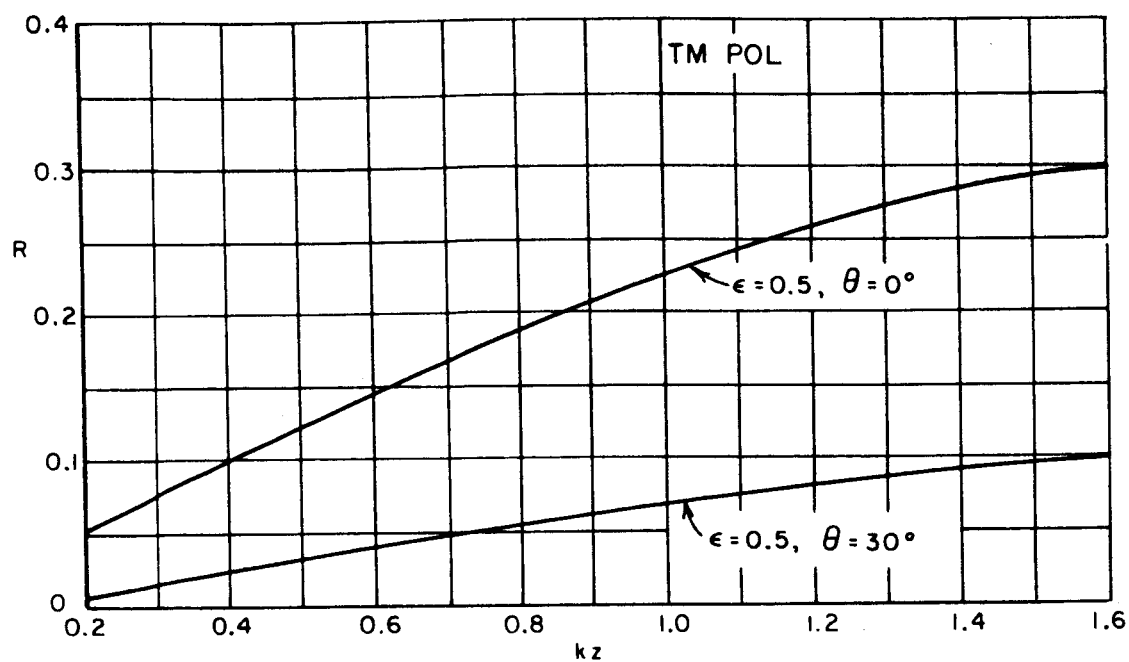


Fig. 18. Reflection coefficient vs layer thickness.

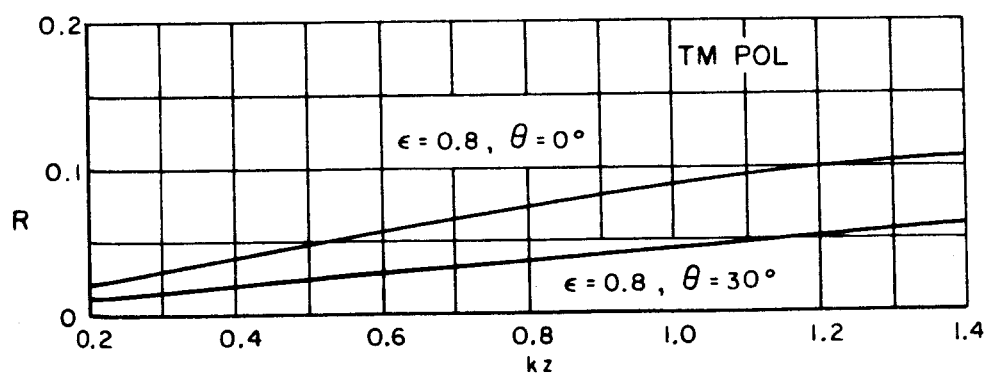


Fig. 19. Reflection coefficient vs layer thickness.

## ELECTRON DENSITY PROFILES

Having examined the equivalent semi-infinite medium technique for slabs of finite thickness and uniform dielectric constant, a varying electron density profile was studied. The electron density profile is that considered by Swift<sup>4</sup> as shown in Fig. 20 along with the associated collision frequency profile. The complex dielectric constants for each frequency are shown in Table I. Data from the profile of Fig. 20 were sampled every 0.1 cm and the frequency was varied from 0.5 to 20.0 GHz. Figures 21 through 25 represent perpendicular or TE polarization and Figs. 26 through 30 represent parallel or TM polarization.

TABLE I  
Complex Dielectric Constant  
for Various Frequencies

Layer	0.5 GHz	3.0 GHz	8.0 GHz	12.0 GHz	20.0 GHz
1	-31.1-j1.53	0.106-j.0071	0.874-j.0003	0.944-j.0001	0.979-j.00002
2	-95.3-j4.59	-1.68-j.021	0.622-j.0011	0.832-j.0003	0.939-j.00007
3	-127.4-j6.13	-2.57-j.028	0.447-j.0015	0.776-j.0005	0.919-j.00009
4	-143.5-j6.89	-3.02-j.032	0.434-j.0016	0.748-j.0003	0.909-j.0001
5	-111.3-j5.36	-2.12-j.024	0.559-j.0013	0.804-j.0003	0.929-j.00008
6	-63.2-j3.06	-0.787-j.014	0.748-j.0007	0.888-j.0002	0.959-j.00004
7	-31.1-j1.53	0.106-j.007	0.874-j.0003	0.944-j.0001	0.979-j.00002
8	-15.05-j0.766	0.533-j.003	0.937-j.0001	0.972-j.00005	0.989-j.00001
9	-7.02-j0.383	0.776-j.0017	0.968-j.00009	0.986-j.00002	0.994-j.000006
10	-2.21-j0.153	0.91-j.0007	0.987-j.00003	0.994-j.00001	0.997-j.000002

Figure 21 shows the reflection as a function of incidence angle at a frequency of 0.5 GHz. The equivalent medium has a dielectric constant of  $\epsilon = 0.000642$  and the critical angle is  $0.48^\circ$ . In this case of very high reflection by the plasma profile the calculated dielectric constants are indeed negative and rapidly varying (see Table I) and the equivalent medium concept is valid only at  $0^\circ$ .

For Fig. 22 the frequency of operation is 3.0 GHz and the computed dielectric profile (shown in Table I) only goes partly negative. The equivalent medium has a dielectric constant of

$\epsilon = 0.110$  and the critical angle is  $19.33^\circ$ . The two reflection coefficient magnitudes correspond for about  $10^\circ$ .

Figure 23 applies for a frequency of 8.0 GHz at which the calculated permittivity is positive and slowly varying throughout the thickness of the plasma slab. The equivalent medium has a dielectric constant of  $\epsilon = 0.475$  and a critical angle of  $43.62^\circ$ . The magnitudes of the reflection coefficients compare favorably for approximately  $30^\circ$ . The equivalent medium concept becomes more useful as frequency increases.

The frequency for Fig. 24 is 12.0 GHz for which the dielectric constant of the equivalent medium is  $\epsilon = 0.6708$  and the critical angle is  $55.58^\circ$ . The computed permittivity of the plasma slab is positive and varies much less than at lower frequencies. The reflection coefficients of the equivalent medium match those of the plasma slab for a range of  $40^\circ$ .

Figure 25 represents the electron density profile at a frequency of 20.0 GHz; and the calculated dielectric constants of the plasma profile vary only very slightly. The equivalent medium has a dielectric constant,  $\epsilon = 0.8832$  and the critical angle is  $70.07^\circ$ . The reflection coefficients of the two media closely correspond for  $60^\circ$ .

Figures 26-30 represent the same frequencies as Figs. 21-25, with the polarization being TM or parallel. The equivalent media and critical angles are the same for frequencies of 0.5, 3.0, 8.0, 12.0, and 20.0 GHz. As in the case of TE or perpendicular polarization the reflection coefficients of the equivalent media and the plasma profile match over wider ranges with increasing frequency. The range of reflection coefficient matching varies from a single point ( $0^\circ$ ) at a frequency of 0.5 GHz to a  $0^\circ$ - $60^\circ$  coincidence for a frequency of 20.0 GHz. The variation in the calculated permittivities range from a rapidly varying negative profile at 0.5 GHz to a very slowly varying positive profile at 20.0 GHz.

Figure 31 shows the variation of reflection coefficient,  $R$ , with frequency for the case of TE or perpendicular polarization and for three different angles of incidence. The greater reflections (almost total) occur at the lower frequencies and gradually decrease to almost zero with increasing frequency.

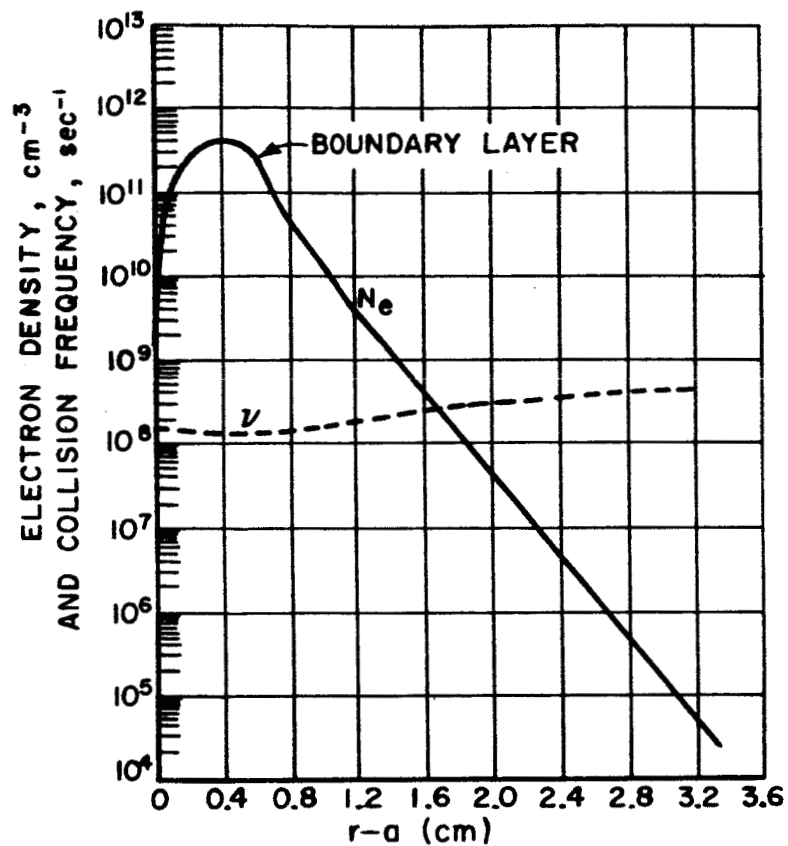


Fig. 20. Electron density and collision frequency profiles for two flow-field assumptions.

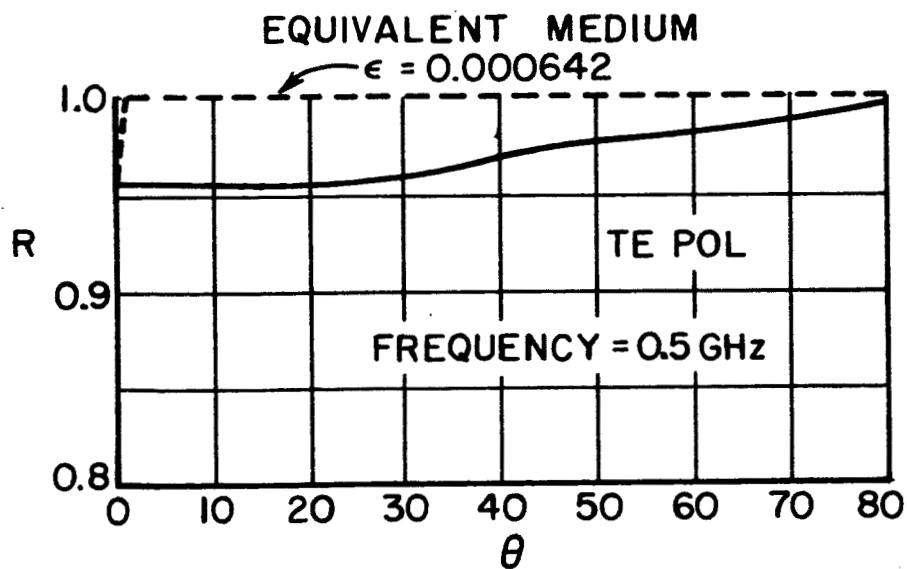


Fig. 21.  $R$  vs  $\theta$  for plasma profile.

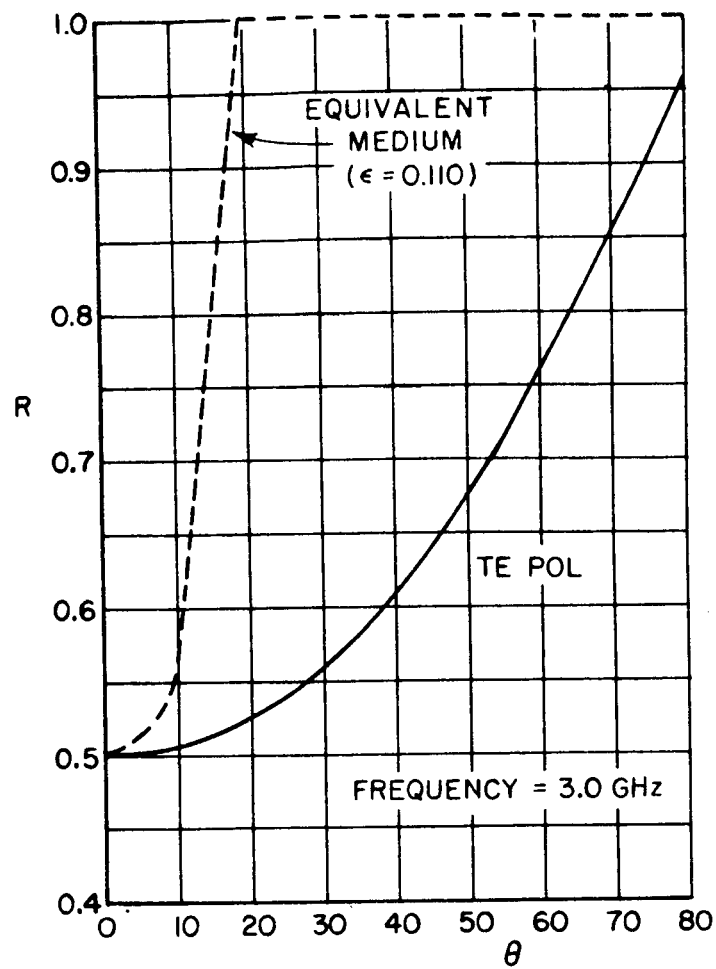


Fig. 22.  $R$  vs  $\theta$  for plasma profile.

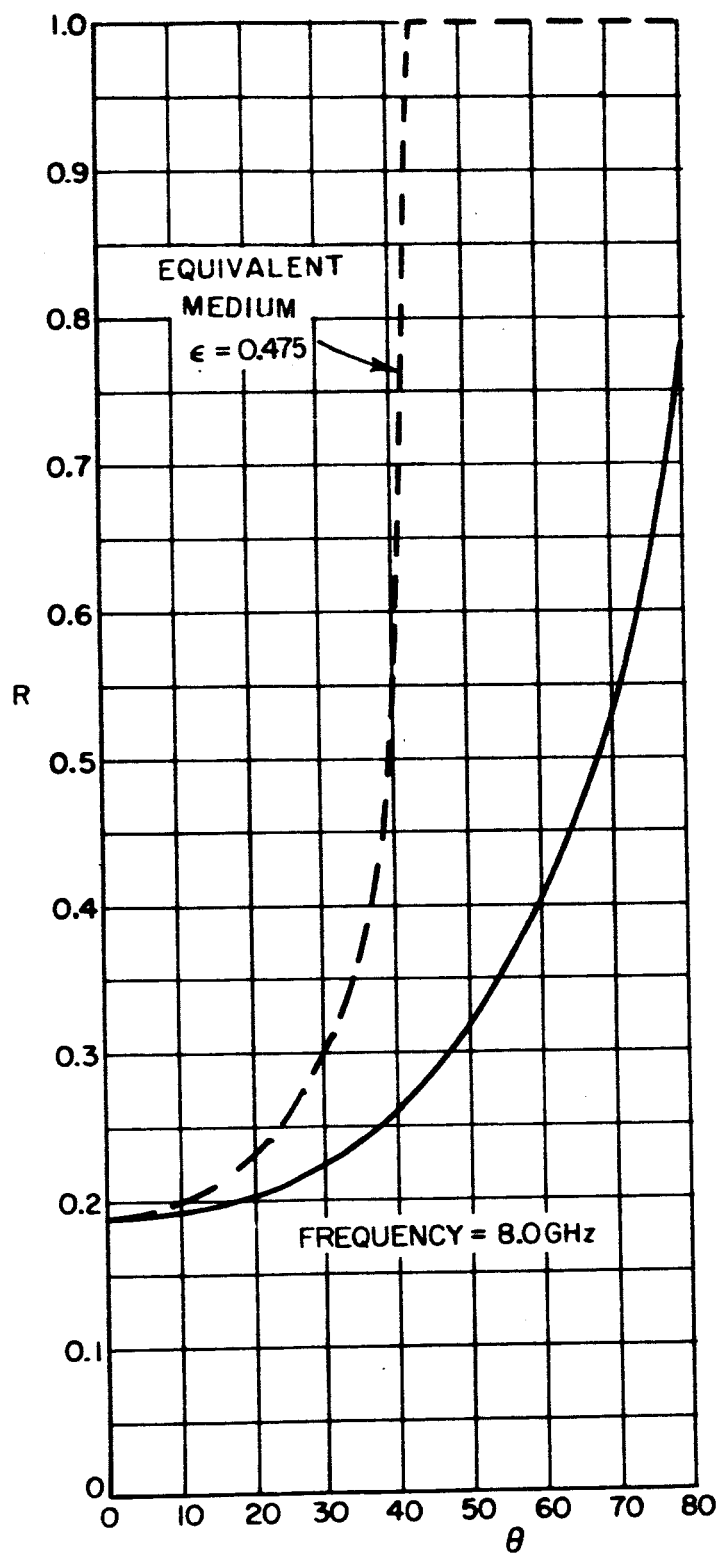


Fig. 23.  $R$  vs  $\theta$  for plasma profile.

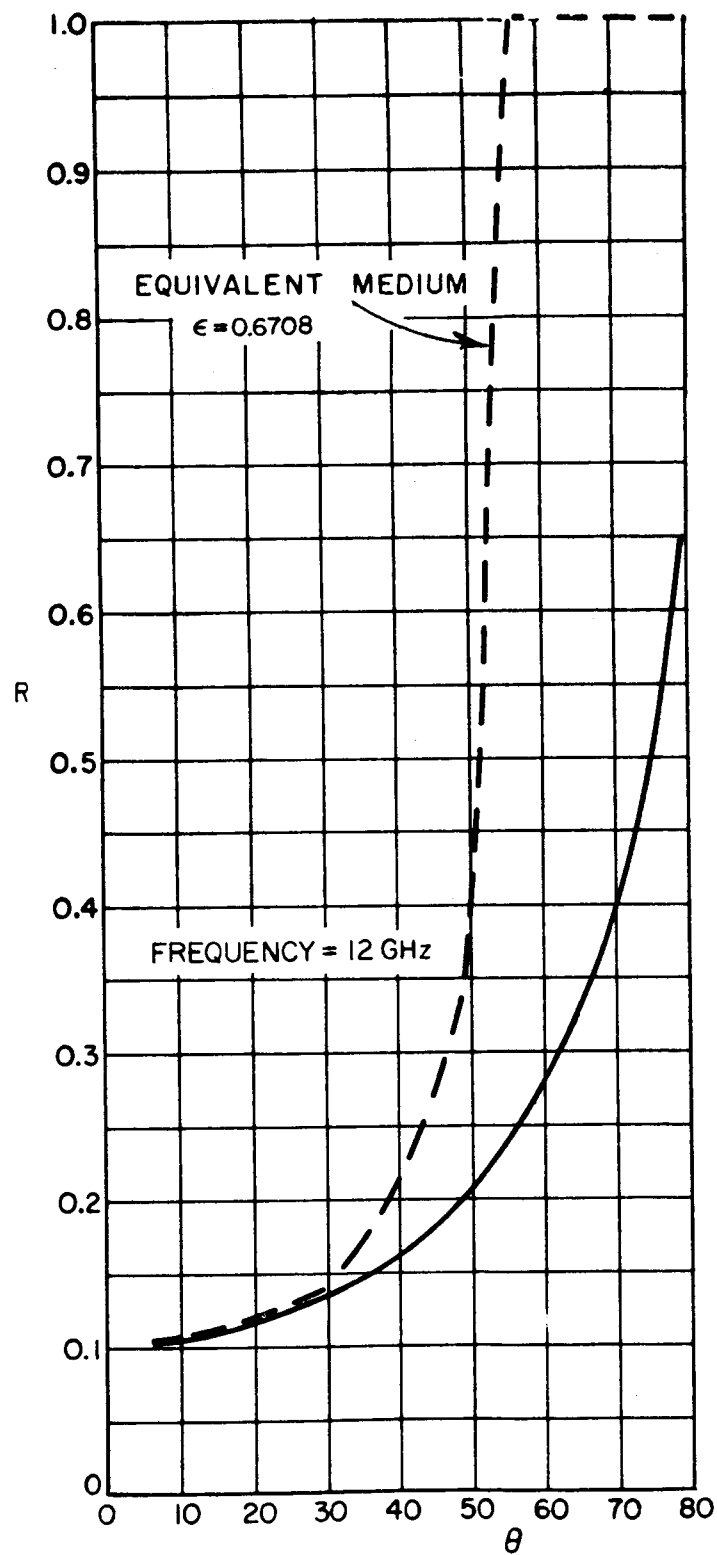


Fig. 24.  $R$  vs  $\theta$  for plasma profile.



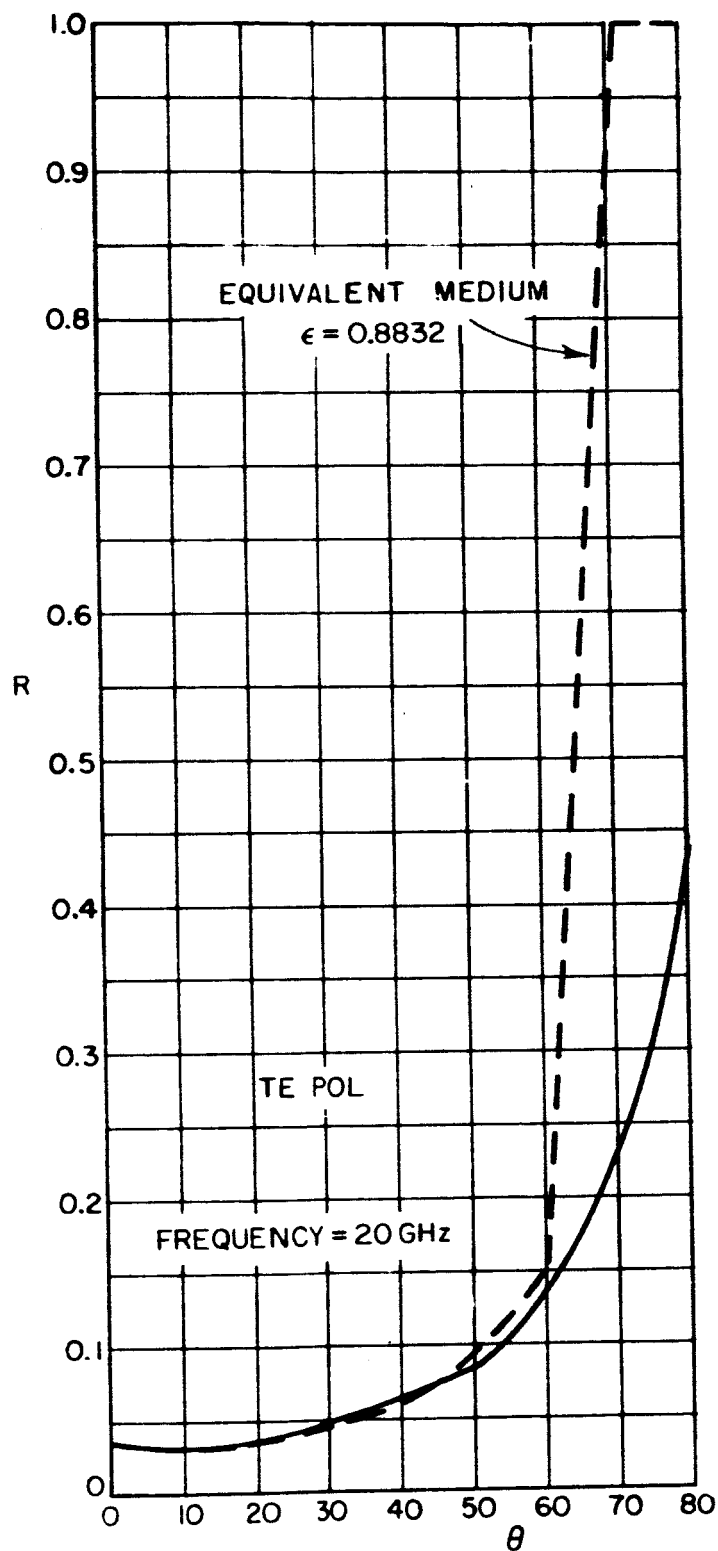


Fig. 25.  $R$  vs  $\theta$  for plasma profile.

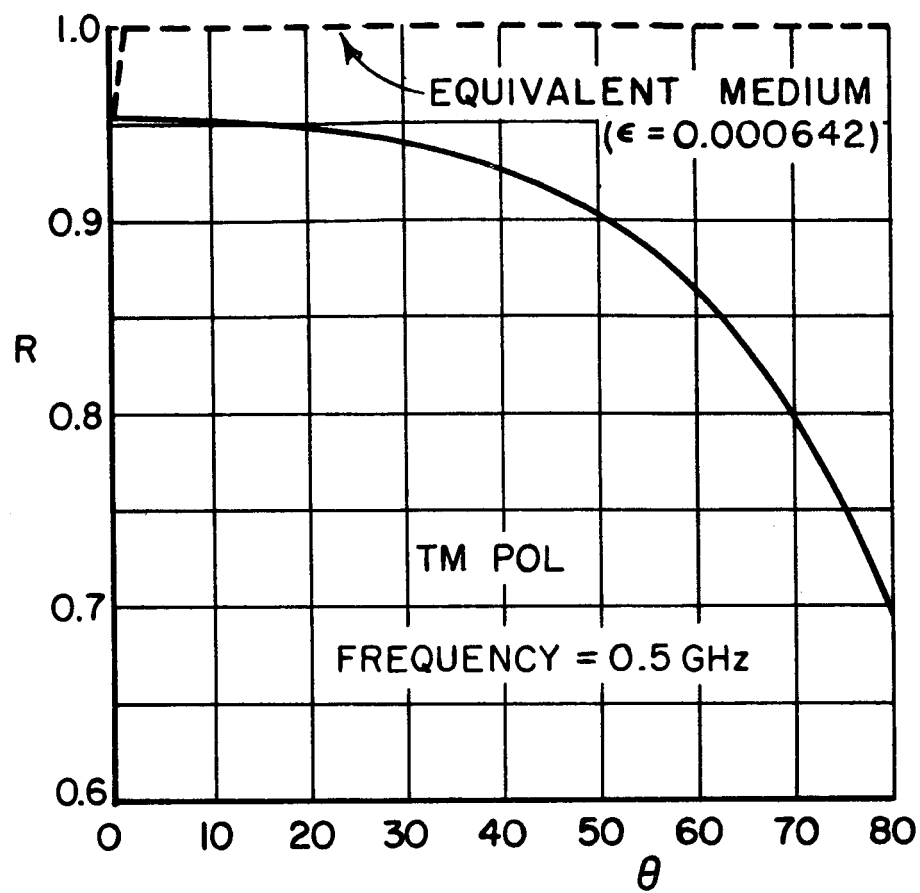


Fig. 26.  $R$  vs  $\theta$  for plasma profile.

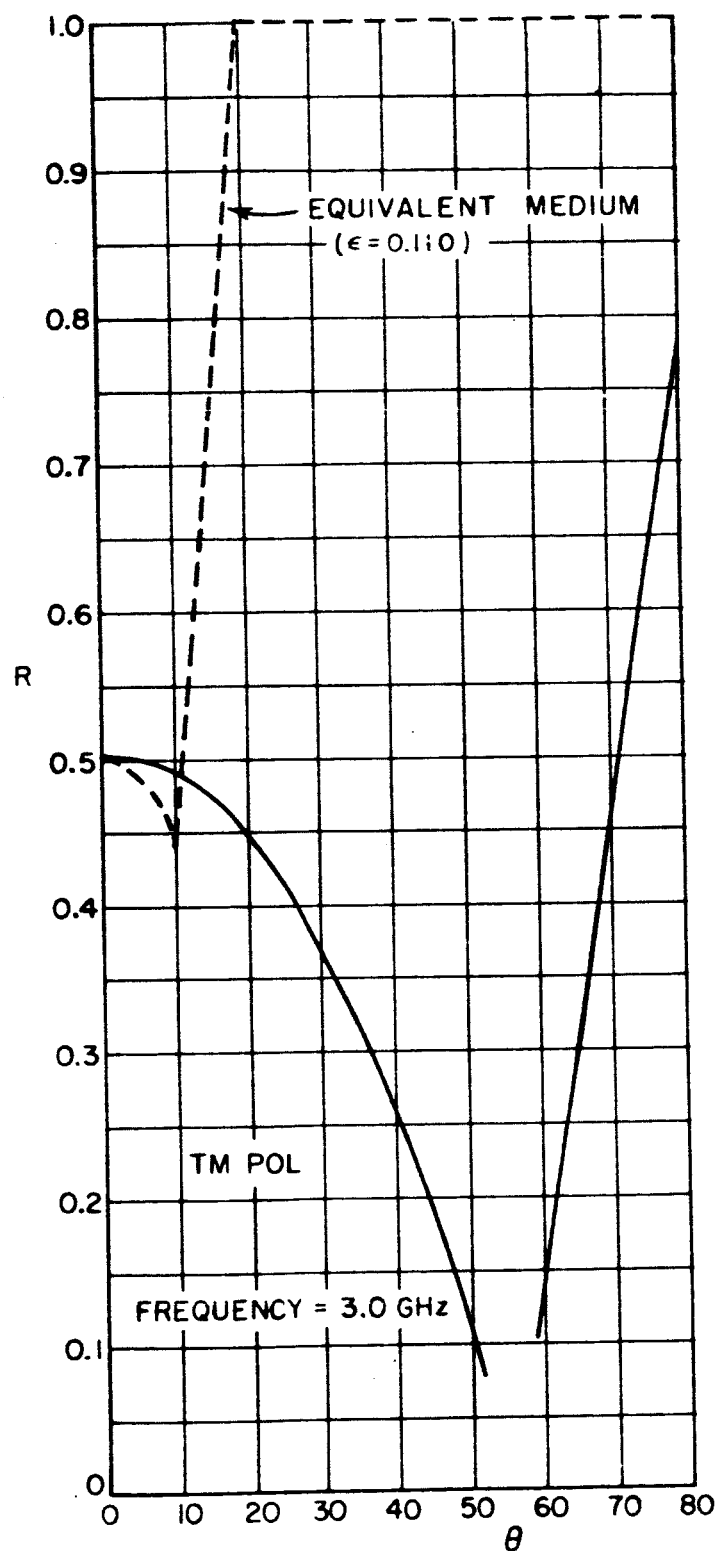


Fig. 27.  $R$  vs  $\theta$  for plasma profile.

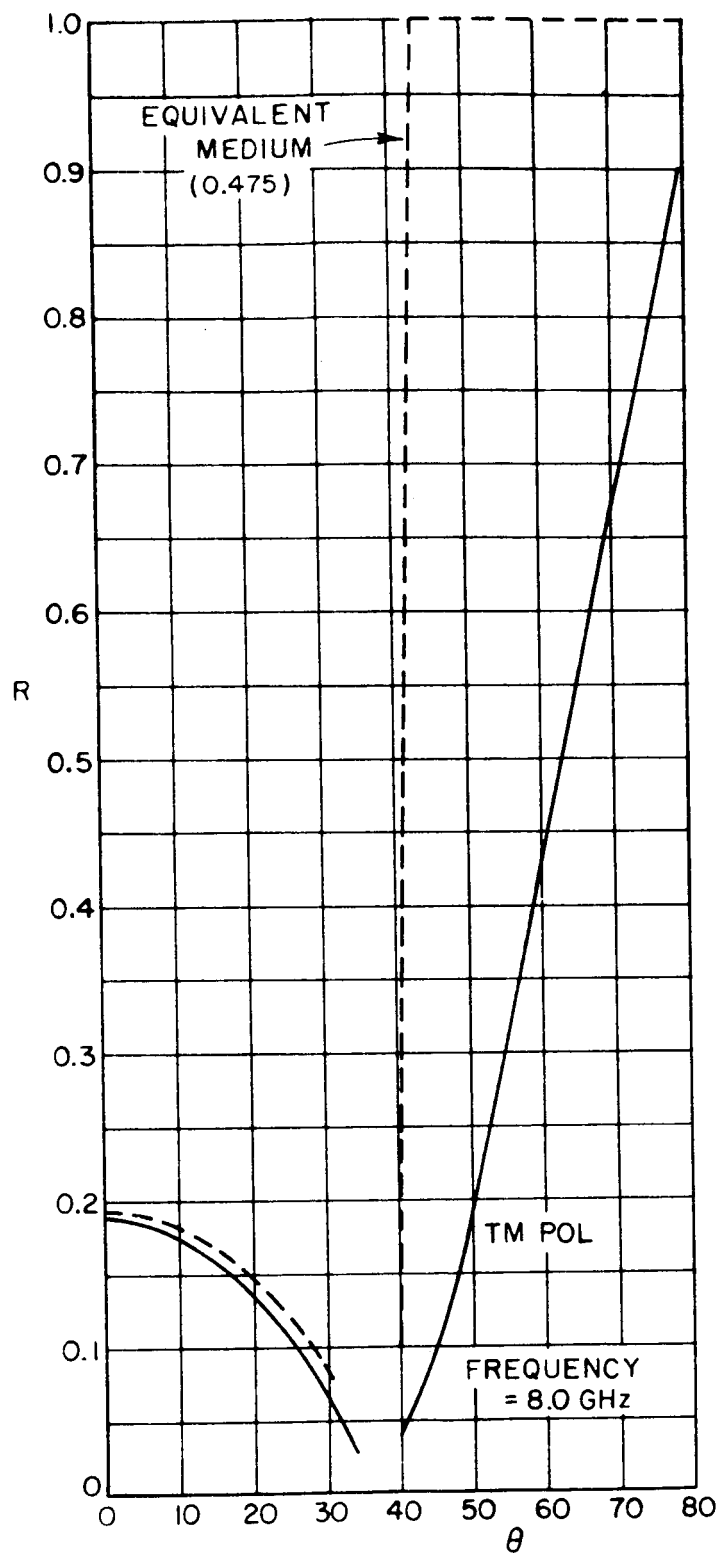


Fig. 28.  $R$  vs  $\theta$  for plasma profile.

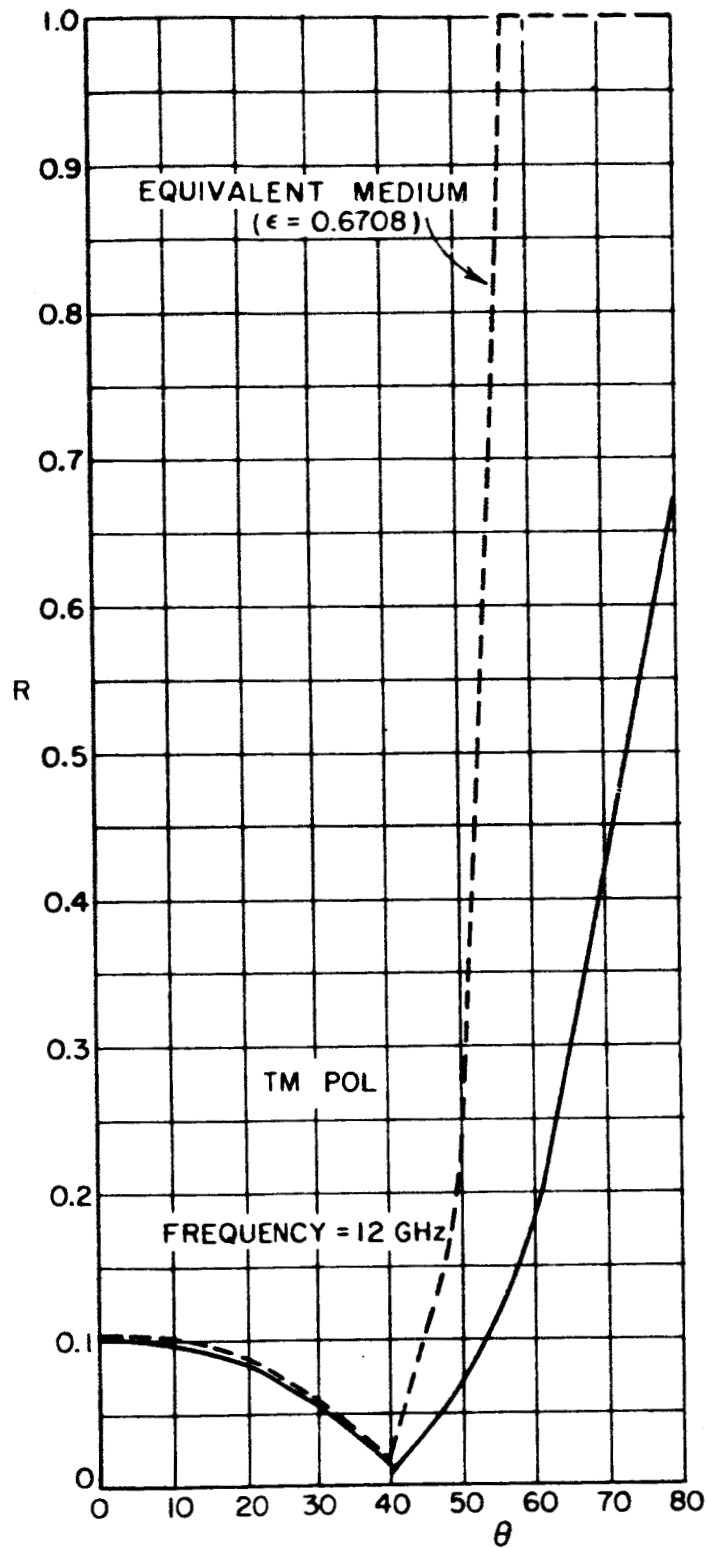


Fig. 29.  $R$  vs  $\theta$  for plasma profile.

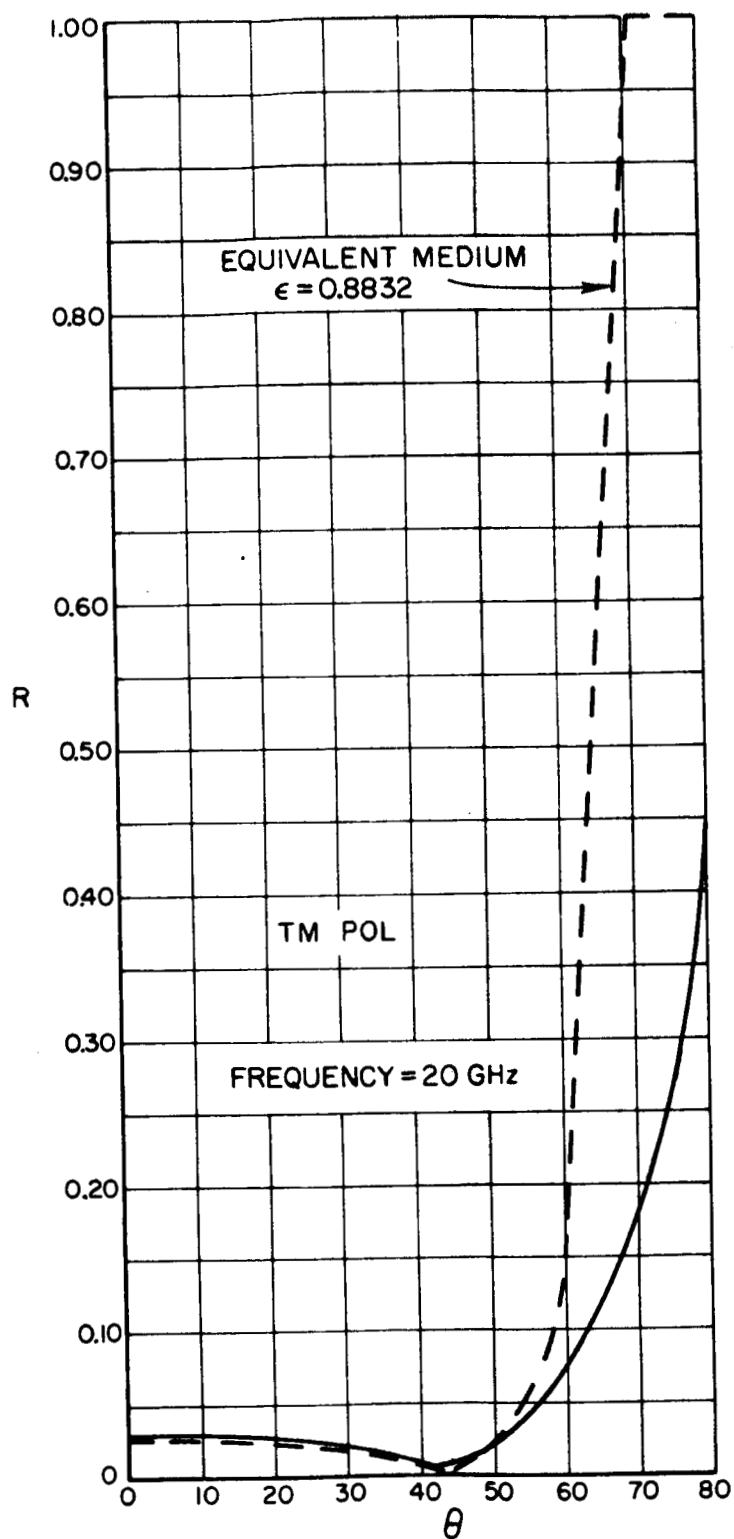


Fig. 30.  $R$  vs  $\theta$  for plasma profile.

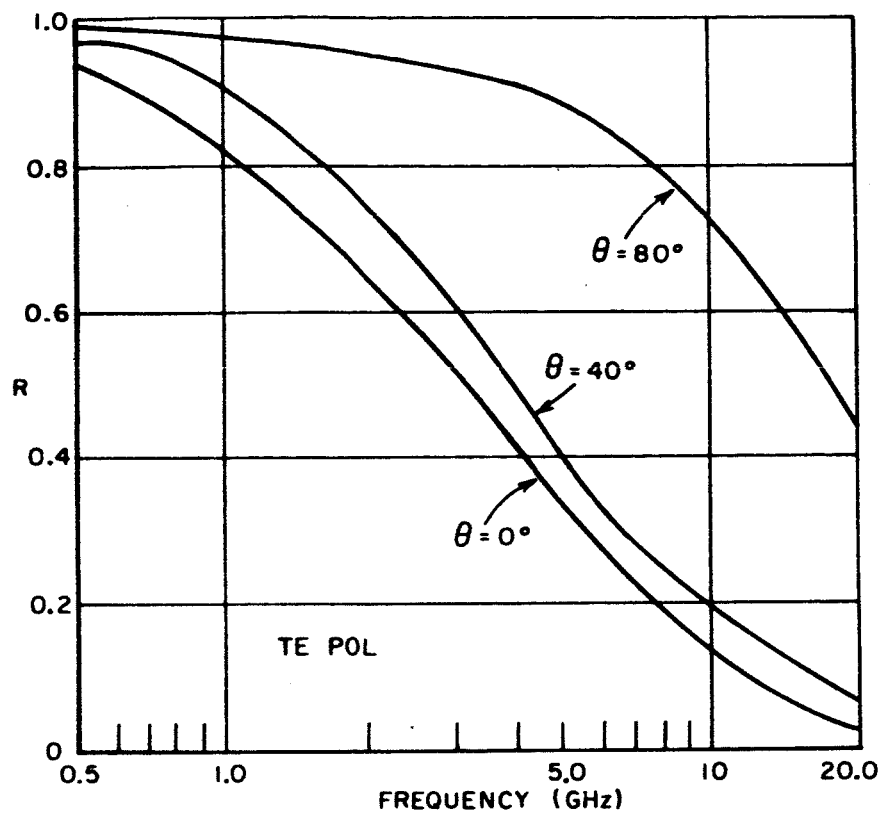


Fig. 31.  $R$  vs frequency for constant angle of incidence.

## CONCLUSIONS

The substitution of an equivalent semi-infinite, homogeneous dielectric medium for an inhomogeneous, finite plasma layer is studied. Comparison of the reflection coefficients as a function of angle of incidence for various media and their equivalent media shows that in most cases there is a range in which the reflection coefficients are approximately equal. It is in this range of agreement that the substitution of the equivalent medium may be effected; the necessary range depends on the particular antenna whose properties are being studied.

The range of equivalence was determined for uniform dielectric slabs of various dielectric constant values and for an inhomogeneous plasma layer at various frequencies. The useful range of equivalence was found to be very narrow (less than  $5^\circ$ ) for cases in which the dielectric constant dips to near or below zero. In other cases fairly wide ranges of equivalence occur.



## APPENDIX A

Figures 32 through 35 give the statement listings of the programs used to calculate reflection coefficients and equivalent media. Figure 32 is the old program for TE polarization. Figure 33 is the old program for TM polarization. Figure 34 is the new program version that uses dielectric constant values as input data. Figure 35 is the new program version that uses the electron density profile as input data.

# SOURCE LANGUAGE STATEMENTS

```

1          COMPLEX (RR,TRM)-
2          DIMENSION (E(16))-
3 F T2      (7F10.5)    -
4 F T3      (15,4F15.8) -
5   S7      READ INPUT ,T3,(N,H,TH)-
6          H2=H*H-
7          READ INPUT ,T2,((E(I),I=1,1,I.LE.N))-
8          M=90./TH-
9          TH=.01745329*TH-
10         THETA=0-
11         DO THROUGH (S31),J=1,1,J.LE.M-
12         S=SIN.(THETA)*SIN.(THETA)-
13         C=COS.(THETA)-
14         R1=1.-
15         S1=0.-
16         I=1-
17         WRITE OUTPUT ,T3,(I,R1,S1,R1)-
18         A=E(1)-S-
19         R2=1.-H2*A/2-H2*(E(2)-E(1))/6.-
20         S2=H*C-H2*H*A*C/6-
21         EMAG=SQRT.(R2*R2+S2*S2)-
22         I=2-
23         WRITE OUTPUT ,T3,(I,R2,S2,EMAG)-
24         DO THROUGH (S25),I=2,1,I.LE.N-
25         I1=I+1-
26         A=E(I)-S-
27         B=2.-H2*A-
28         R3=P*R2-R1-

```

Fig. 32. TE polarizations.

```

29          S3=R*S2-S1-
30          EMAG=SQRT.(R3*R3+S3*S3)-
31          WRITE OUTPUT ,T3,(I1,R3,S3,EMAG)-
32          TRANSFER TO (S32,S28,S20) PROVIDED (N-1)-
33  S20      R1=R2-
34          S1=S2-
35          R2=R3-
36  S25      S2=S3-
37  S28      DRR=SQRT.(E(N))*H*C*2.*R2-S3+S1-
38          DRI=SQRT.(E(N))*H*C*2.*S2+R3-R1-
39          DDR=SQRT.(E(N))*H*C*2.*R2+S3-S1-
40          DDI=SQRT.(E(N))*H*C*2.*S2-R3+R1-
41          RR=(DRR+.1.DRI)/(DDR+.1.DDI)-
42          RMAG=.ABS.(RR)-
43          ANDN=FATAN2.(DRR,DRI)-
44          ANDD=FATAN2.(DDR,DDI)-
45          ANG=ANDN-ANDD-
46  S30      ANG=ANG*57.29578-
47          TRM=(4.*H*C)/(DDR+.1.DDI)-
48          TRMAG=.ABS.(TRM)-
49          THD=57.29578*THETA-
50          WRITE OUTPUT ,T2,(RMAG,ANG,THD,TRMAG)-
51  S31      THETA=THETA+TH-
52  S32      CALL SUBROUTINE ()=ENDJOB.()-
53          END PROGRAM (S7)-

```

Fig. 32(cont.)

# SOURCE LANGUAGE STATEMENTS

```

1  S1      COMPLEX (H1,H2,H3,F1,F2,F3,RR,TP,A,B,CC,E(40))-
2          COMPLEX (RRT)-
3          COMPLEX (CSQRTL.)-
4  F T2    (7F10.5)  -
5  F T3    (15,6F10.5) -
6  S7      READ INPUT ,T3,(N,Z,TH)-
7  START   READ INPUT ,IN1,(NUMCAS)-
8  F IN1    (12)  -
9          Z2=Z*Z-
10         M=90/TH-
11         TH=.01745329*TH-
12  GO      NUMCAS=NUMCAS-1-
13         READ INPUT ,T2,((E(I),I=1,1,1.LE.N))-
14         THETA=0-
15         DO THROUGH (S31),L=1,1,L.LE.M-
16         S=SIN.(THETA)*SIN.(THETA)-
17         C=COS.(THETA)-
18         H1=1.-
19         F1=C-
20         I=1-
21         WRITE OUTPUT ,T3,(I,H1,F1)-
22         EI=.IMAG.(E(1))-
23         ER=.REAL.(E(1))-
24         EER=.REAL.(E(2))-
25         WRITE OUTPUT ,T2,(ER,EI,EER)-
26         F2=C+Z*S*EI/(ER*ER)-Z2/2*(ER-S)*C+.1.(Z*(1-S/ER+Z/2*EI*C-1./6.
27         H2=1-Z*EI*C-Z2/2*(ER-S)+.1.(7*(FR*C+Z*EI/2-1./6.*Z2*ER*(ER-S)*C))-
28         H2A=.ABS.(H2)-

```

Fig. 33. TM polarizations.

```

29      F2A=.ABS.(F2)-
30      RR=(H2*C-F2)/(H2*C+F2)-
31      RRMAG=.ABS.(RR)-
32      TR=2/(H2+F2/C)-
33      TRMAG=.ABS.(TR)-
34      I=2-
35      WRITE OUTPUT ,T3,{1,H2A,F2A,RRMAG,TRMAG}-
36      WRITE OUTPUT ,T2,(RR,TR)-
37      WRITE OUTPUT ,T2,(H2,F2)-
38      DO THROUGH (S25),I=2,1,I.LE.N-
39      II=I+1-
40      CC=E(I)-E(I-1)-
41      K=100-
42      PROVIDED (I.E.2),K=99-
43      DO THROUGH (S21),J=1,1,J.LE.K-
44      EE=E(I-1)+J*CC/100.-
45      A=EE-S-
46      B=2.-Z2*A-
47      F3=B*F2-F1+.1.(Z*CC*S*H2/(100*EE*EE))-
48      H3=B*H2-H1+.1.(Z*CC*F2/100.)-
49      F1=F2-
50      F2=F3-
51      H1=H2-
52      S21      H2=H3-
53      RR=(H3*C-F3)/(H3*C+F3)-
54      TR=2*C/(H3*C+F3)-
55      F3A=.ABS.(F3)-
56      H3A=.ABS.(H3)-
57      RRMAG=.ABS.(RR)-

```

Fig. 33(cont.)

```

58      TRMAG=.ABS.(TR)-
59      THD=57.29578*THETA-
60      TRANSFER TO (S27,S28,S29) PROVIDED (.REAL.(E(1)))-
61 S27    RRT=(H3*C-.I.(CSQRTL.(E(1))*F3))/(H3*C+.I.(CSQRTL.(E(1))*F3))-
62      TRANSFER TO (S30)-
63 S28    RRT=1.-
64      TRANSFER TO (S30)-
65 S29    RRT=(H3*C-CSQRTL.(E(1))*F3)/(H3*C+CSQRTL.(E(1))*F3)-
66 S30    RRTM=.ABS.(RRT)-
67      WRITE OUTPUT ,T3,(11,H3A,F3A,RRMAG,TRMAG,THD)-
68      WRITE OUTPUT ,T2,(RR,TR,RRT,THD)-
69      WRITE OUTPUT ,T2,(H3,F3)-
70 S25    WRITE OUTPUT ,T2,(RRTM)-
71 S31    THETA=THETA+TH-
72 S32    PROVIDED (NUMCAS.G.O), TRANSFER (GO)-
73 S33    CALL SUBROUTINE ()=ENDJOB.()-
74      END PROGRAM (S7)-

```

Fig. 33(cont.)

```

1      COMPLEX (CSQRTL.,CEXPL.,CI,EC,G,AE,AB,BE,BM,GZ,F,YI,YII,EXPI,
          EXPII, AEP,AMP,EXP,RE,RM,FP,FM,TE,TH)-
2      COMPLEX (UC(100),EC(100),G(100))-
3      COMPLEX (AM)-
4      COMPLEX (SQR)-
5      COMPLEX (AET,AMT,BET,BMT,EXP3)-
6      COMPLEX (FT)-
7      COMPLEX (RQTE,RQTM)-
8      DIMENSION (Z(100))-
9  FIRST READ INPUT ,8,(KKK,N)-
10      READ INPUT ,7,(D,TH)-
11      DR=57.295779-
12      DO THROUGH (S10),I=1,1,I.LE.N-
13  S10  UC(I)=1.-
14      NN=N+1-
15      EC(NN)=1.-
16      UC(NN)=1.-
17      TPI=6.2831853-
18      CI=.1.1.-
19      M=90/TH-
20      Z(0)=.0-
21      DO THROUGH (S30),I=1,1,I.LE.N-
22      II=I-1-
23  S30  Z(I)=Z(II)+D-
24      DO THROUGH (S100),K=1,1,K.LE.KKK-
25      READ INPUT ,7,((EC(I),I=1,1,I.LE.N))-
26      THETA=0-
27      WRITE OUTPUT ,F4,((I,Z(I),EC(I),I=1,1,I.LE.N))-
28 F F4  (16Y,13,5X,F15.8,10X,2E15.7) -

```

Fig. 34. New program. Dielectric constant version.

```

29      DO THROUGH (S99),J=1,1,J.LE.M-
30      THET=0.01745329*THETA-
31      SS=SIN.(THET)*SIN.(THET)-
32      CC=COS.(THET)-
33      DO THROUGH (S40),II=1,1,II.LE.N-
34  S40  G(II)=CSQRTL.(SS-EC(II))-
35      GZ=CI*CC-
36      G(NN)=CI*CC-
37      AET=.5*(1.+UC(1)*GZ/G(1))-
38      BET=.5*(1.-UC(1)*GZ/G(1))-
39      AMT=.5*(1.+EC(1)*GZ/G(1))-
40      BMT=.5*(1.-EC(1)*GZ/G(1))-
41      WRITE OUTPUT ,F5,(THETA)-
42 F F5  (///30X,6HTHETA=,F15.8//6H LAYER,9X,5HGAMMA,22X,2HAE,20X,
        2HBE,20X,2HAM,20X,2HBM/)-
43      J1=1-
44      WRITE OUTPUT ,F6,(J1,G(1),AET,BET,AMT,BMT)-
45 F F6  (1X,I3,2E14.6,8E11.3) -
46      DO THROUGH (S50),II=2,1,II.LE.N-
47      I=II-1-
48      F=UC(II)*G(1)/(UC(II)*G(II))-
49      YI=G(1)*Z(1)-
50      YII=G(II)*Z(1)-
51      FP=1.+F-
52      FM=1.-F-
53      EXPI=CEXP.(YI)-
54      EXPYII=CEXP.(YII)-
55      AEP=AET-
56      AMP=AMT-
57      ALT=.5/EXPI*(AEP*EXPI*FP+BET*FM/EXPI)-

```

Fig. 34(cont.)



```

58      RET=0.5*EXP11*(AET*EXPI*FM+RET*FP/EXPI)-
59      EXP3=CEXP1.(CI*CC*Z(1))-
60      FP=1.+G(1)/(CI*CC)-
61      FM=1.-G(1)/(CI*CC)-
62      AE=.5/EXP3*(AET*EXPI*FP+RET*FM/EXPI)-
63      RE=0.5*EXP3*(AET*EXPI*FM+RET*FP/EXPI)-
64      F=EC(11)*G(1)/(EC(1)*G(11))-
65      FP=1.+F-
66      FM=1.-F-
67      AMT=(.5/EXP11)*(AMP*EXPI*FP+BMT*FM/EXPI)-
68      RMT=.5*EXP11*(AMP*EXPI*FM+BMT*FP/EXPI)-
69      FT=G(1)/(EC(1)*CI*CC)-
70      FP=1.+FT-
71      FM=1.-FT-
72      AM=.5/EXP3*(AMT*EXPI*FP+BMT*FM/EXPI)-
73      RM=.5*EXP3*(AMT*EXPI*FM+BMT*FP/EXPI)-
74      WRITE OUTPUT ,F6,(11,G(11),AE,BE,AM,HM)-
75      TE=1./AE-
76      TM=1./AM-
77      ARG=2.*CC*Z(N)-
78      EXP=COS.(ARG)-.I.SIN.(ARG)-
79      RE=EXP*BE/AE-
80      RM=EXP*FM/AM-
81      TEM=.ABS.TE-
82      TMM=.ABS.TM-
83      REM=.ABS.RE-
84      RMM=.ABS.RM-
85      FIPDE=-DR*FATAN2.(.IMAG.TE,.REAL.TE)-
86      FIPDM=-DR*FATAN2.(.IMAG.TM,.REAL.TM)-

```

Fig. 34(cont.)

```

87      PRE=DR*FATAN2.(.IMAG.RE,.REAL.RE)-
88      PRM=DR*FATAN2.(.IMAG.RM,.REAL.RM)-
89      WRITE OUTPUT ,F11-
90 F F11      (///22X,9HMAGNITUDE,14X,5HPHASE,15X,4HREAL,16X,4HIMAG/)
91      WRITE OUTPUT ,F7,(REM,PRE,RE)-
92 F F7      (1X,13HTE REFLECTION,6X,2(F15.8,5X),2(E15.7,5X))-
93      WRITE OUTPUT ,F8,(TEM,FIPDM,TM)-
94 F F8      (1X,15HTE TRANSMISSION,4X,2(F15.8,5X),2(E15.7,5X)) -
95      WRITE OUTPUT ,F9,(RMM,PRM,RM)-
96 F F9      (1X,13HTM REFLECTION,6X,2(F15.8,5X),2(E15.7,5X))-
97 S50      WRITE OUTPUT ,F10,(TMM,FIPDM,TM)-
98 F F10      (1X,15HTM TRANSMISSION,4X,2(F15.8,5X),2(E15.7,5X)) -
99      PROVIDED (THETA.G.O.), TRANSFER (SX)-
100      EQTE=((1.-REM)/(1.+REM)).P.2-
101      EQTM=((1.-RMM)/(1.+RMM)).P.2-
102      DQTE=-PRE/720.-
103      DEL=PRM/.ABS.(PRM)-
104      DQTM=(PRM-DEL*180.)/720.-
105      WRITE OUTPUT ,F12,(EQTE,DQTE,EQTM,DQTM)-
106 F F12      (/50X,17HEQUIVALENT MEDIUM/5X,5HEQTE=,F15.8,5X,5HDQTE=,
              F15.8,5X,5HEQTM=,F15.8,5X,5HDQTM=,F15.8)
107 SX      SQR=CSQRTL.(EQTE-SS)-
108      RQTE=(CC-SQR)/(CC+SQR)-
109      PQTE=-720.*DQTE*CC-
110      SQR=CSQRTL.(EQTM-SS)-
111      PQTM=720.*DQTM*CC+DEL*180.-
112      RQTM=(EQTM*CC-SQR)/(EQTM*CC+SQR)-
113      WRITE OUTPUT ,F13,(RQTE,PQTE,RQTM,PQTM)-
114 F F13      (15X,5HRQTE=,2F15.7,5X,5HPQTE=,F15.7/5X,5HRQTM=,2E15.7,
              5X,5HPQTM=,E15.7) -
115 S99      THETA=THETA+TH-

```

Fig. 34(cont.)

# SOURCE LANGUAGE STATEMENTS

```

1      COMPLEX (CSQRTL.,CEXPI.,CI.FC.G.AE,AB,BE,BM,GZ,F,YI,YII,
           EXPI,EXPII,AEP,AMP,EXP,RE,RM,FP,FM,TE,TM)-
2      COMPLEX (UC(100),EC(100),G(100))-
3      COMPLEX (AM)-
4      COMPLEX (SQR)-
5      COMPLEX (RQTE,RQTM)-
6      COMPLEX (ARGG)-
7      DIMENSION (FNE(100),FNU(100),Z(100))-
8 FIRST READ INPUT ,8,(KKK,N)-
9      READ INPUT ,7,(D,TH)-
10     READ INPUT ,6,((FNE(I),I=1,1,I.LE.N))-
11     READ INPUT ,6,((FNU(I),I=1,1,I.LE.N))-
12     DR=57.295779-
13     WRITE OUTPUT ,F1-
14     WRITE OUTPUT ,F2,((I,FNE(I),FNU(I),I=1,1,I.LE.N))-
15 F F1  (///40X,24HELECTRON DENSITY PROFILE//32X,5HLAYER,7X,
           7HDENSITY,10X,9HCOLLISION/)
16 F F2  (33X,13,4X,E15.7,4XE15.7) -
17     DO THROUGH (S10),I=1,1,I.LE.N-
18 S10   UC(I)=1.-
19     NN=N+1-
20     TPI=6.2831853-
21     CI=.I.I.-
22     EC(NN)=1.-
23     UC(NN)=1.-
24     M=90/TH-
25     Z(0)=.0-
26     DO THROUGH (S100),K=1,1,K.LE.KKK-
27     READ INPUT ,7,(FGC)-
28     WAVE=30./FGC-

```

Fig. 35. New program. Electron density profile version.

```

29      DO THROUGH (S30),I=1,1,I.LE.N-
30      II=I-1-
31  S30    Z(II)=Z(II)+D*TPI/WAVE-
32      DO THROUGH (S25),I=1,1,I.LE.N-
33      FPL=8.97*SQRT.(FNE(I))*10.P.3-
34      X=FNU(I)/(TPI*FPL)-
35      Y=FGC/FPL*10.P.9-
36      DEN=X*X+Y*Y-
37      EC(I)=1.-1./DEN-.I.(X/(Y*DEN))-
38      WRITE OUTPUT ,1,(X,Y,DEN,FPL)-
39  S25    CONTINUE -
40      THETA=0-
41      WRITE OUTPUT ,F3,(FGC,WAVE)-
42      WRITE OUTPUT ,F4,((I,Z(I),EC(I),I=1,1,I.LE.N))-
43 F F3    (///30X,10HFREQUENCY=,F15.8,3HGC.,7X,11HWAVELENGTH=,
          F15.8,3HCM.//5X,5HLAYER,20X,2HKZ,26X,12HPERMITTIVITY/)
44 F F4    (16X,I3,5X,F15.8,10X,2E15.7) -
45      DO THROUGH (S99),J=1,1,J.LE.M-
46      THET=0.01745329*THETA-
47      SS=SIN.(THET)*SIN.(THET)-
48      CC=COS.(THET)-
49      DO THROUGH (S40),II=1,1,II.LE.N-
50      ARGG=SS-EC(II)-
51      G(II)=CSQRTL.(ARGG)-
52  S40    WRITE OUTPUT ,1,(THET,SS,CC,G(II),EC(II))-
53      GZ=C1*CC-
54      G(NN)=C1*CC-
55      AE=.5*(1.+UC(1)*GZ/G(1))-
56      BE=.5*(1.-UC(1)*GZ/G(1))-
57      AM=.5*(1.+EC(1)*GZ/G(1))-

```

Fig. 35(cont.)

```

58      BM=.5*(1.-EC(1)*GZ/G(1))-
59      WRITE OUTPUT ,F5,(THETA)-
60 F F5      (///30X,6HTHETA=,F15.8//6H LAYER,9X,5HGAMMA.
61           22X,2HAE,20X,2HBE,20X,2HAM,20X,2HBM/)
62      J1=1-
63      WRITE OUTPUT ,F6,(J1,G(1),AE,BE,AM,BM)-
64 F F6      (1X,I3,2E14.6,8E11.3) -
65      DO THROUGH (S50),II=2,1,II.LE.NN-
66      I=II-1-
67      F=UC(II)*G(I)/(UC(I)*G(II))-
68      YI=G(I)*Z(I)-
69      YII=G(II)*Z(I)-
70      FP=1.+F-
71      FM=1.-F-
72      EXPI=CEXP.(YI)-
73      EXP II=CEXP.(YII)-
74      AEP=AE-
75      AMP=AM-
76      AE=(.5/EXPII)*(AEP*EXPI*FP+BE*FM/EXPI)-
77      BE=.5*EXPII*(AEP*EXPI*FM+BE*FP/EXPI)-
78      F=EC(II)*G(I)/(EC(I)*G(II))-
79      FP=1.+F-
80      FM=1.-F-
81      AM=(.5/EXPII)*(AMP*EXPI*FP+BM*FM/EXPI)-
82      BM=.5*EXPII*(AMP*EXPI*FM+BM*FP/EXPI)-
83      WRITE OUTPUT ,F6,(II,G(II),AE,BE,AM,BM)-
84 S50      CONTINUE -
85      TE=1./AE-
86      TM=1./AM-
87      ARG=2.*CC*Z(N)-

```

Fig. 35(cont.)

```

87      EXP=COS.(ARG)-.I.SIN.(ARG)-
88      RE=EXP*BE/AE-
89      RM=EXP*BM/AM-
90      TEM=.ABS.TE-
91      TMM=.ABS.TM-
92      REM=.ABS.RE-
93      RMM=.ABS.RM-
94      FIPDE=-DR*FATAN2.(.IMAG.TE,.REAL.TE)-
95      FIPDM=-DR*FATAN2.(.IMAG.TM,.REAL.TM)-
96      PRE=DR*FATAN2.(.IMAG.RE,.REAL.RE)-
97      PRM=DR*FATAN2.(.IMAG.RM,.REAL.RM)-
98      WRITE OUTPUT ,F11-
99 F F11      (///22X,9HMAGNITUDE,14X,5HPHASE,15X,4HREAL,16X,4HIMAG/) -
100      WRITE OUTPUT ,F7,(REM,PRE,RE)-
101 F F7      (1X,13HTE REFLECTION,6X,2(F15.8,5X),2(E15.7,5X))-
102      WRITE OUTPUT ,F8,(TEM,FIPDE,TE)-
103 F F8      (1X,15HTE TRANSMISSION,4X,2(F15.8,5X),2(E15.7,5X)) -
104      WRITE OUTPUT ,F9,(RMM,PRM,RM)-
105 F F9      (1X,13HTM REFLECTION,6X,2(F15.8,5X),2(E15.7,5X))-
106      WRITE OUTPUT ,F10,(TMM,FIPDM,TM)-
107 F F10     (1X,15HTM TRANSMISSION,4X,2(F15.8,5X),2(E15.7,5X)) -
108      PROVIDED (THETA.G.O.), TRANSFER (SX)-
109      EQTE=((1.-REM)/(1.+REM)).P.2-
110      EQTM=((1.-RMM)/(1.+RMM)).P.2-
111      DQTE=-PRE/720.-
112      DEL=PRM/.ABS.(PRM)-
113      DQTM=(PRM-DEL*180.)/720.-
114      WRITE OUTPUT ,F12,(EQTE,DQTE,EQTM,DQTM)-
115 F F12     (/50X,17HEQUIVALENT MEDIUM/5X,5HEQTE=,F15.8,5X,5HDQTE=,
-           F15.8,5X,5HEQTM=,F15.8,5X,5HDQTM=,F15.8)

```

Fig. 35(cont.)

```

116  SX      SQR=CSQRTL.(EQTE-SS)-
117          RQTE=(CC-SQR)/(CC+SQR)-
118          PQTE=-720.*DQTE*CC-
119          SQR=CSQRTL.(EQTM-SS)-
120          PQTM=720.*DQTM*CC+DEL*180.-
121          RQTM=(EQTM*CC-SQR)/(EQTM*CC+SQR)-
122          WRITE OUTPUT ,F13,(RQTE,PQTE,RQTM,PQTM)-
123 F F13    (15X,5HRQTE=,2E15.7,5X,5HPQTE=,E15.7/5X,5HROTM=
124 S99      THETA=THETA+TH-      ,2E15.7,5X, 5HPQTM=,E15.7) -
125 S100     WRITE OUTPUT ,2-
126          END PROGRAM (FIRST)-

```

Fig. 35(cont.)

## REFERENCES

1. Compton, R. T., Jr., "The Aperture Admittance of a Rectangular Waveguide Radiating Into a Lossy Half-Space," Report 1691-1, 30 September 1963, Antenna Laboratory, The Ohio State University Research Foundation; prepared under Grant Number NsG-448 for National Aeronautics and Space Administration.
2. Richmond, J. H., "Transmission Through Inhomogeneous Plane Layers," Report 1180-4, 15 July 1961, Antenna Laboratory, The Ohio State University Research Foundation; prepared under Contract AF 33(616) -7614 for Aeronautical Systems Division, Wright-Patterson Air Force Base, Ohio. (AD 261 109)
3. Personal correspondence and unpublished notes, J. Richmond, July 1965, Antenna Laboratory, Department of Electrical Engineering, The Ohio State University, Columbus, Ohio.
4. Swift, C. T., "Radiation Patterns of a Slotted-Cylinder Antenna in the Presence of an Inhomogeneous Lossy Plasma," IEEE Transactions on Antennas and Propagation, Vol. AP-12, November 1964.